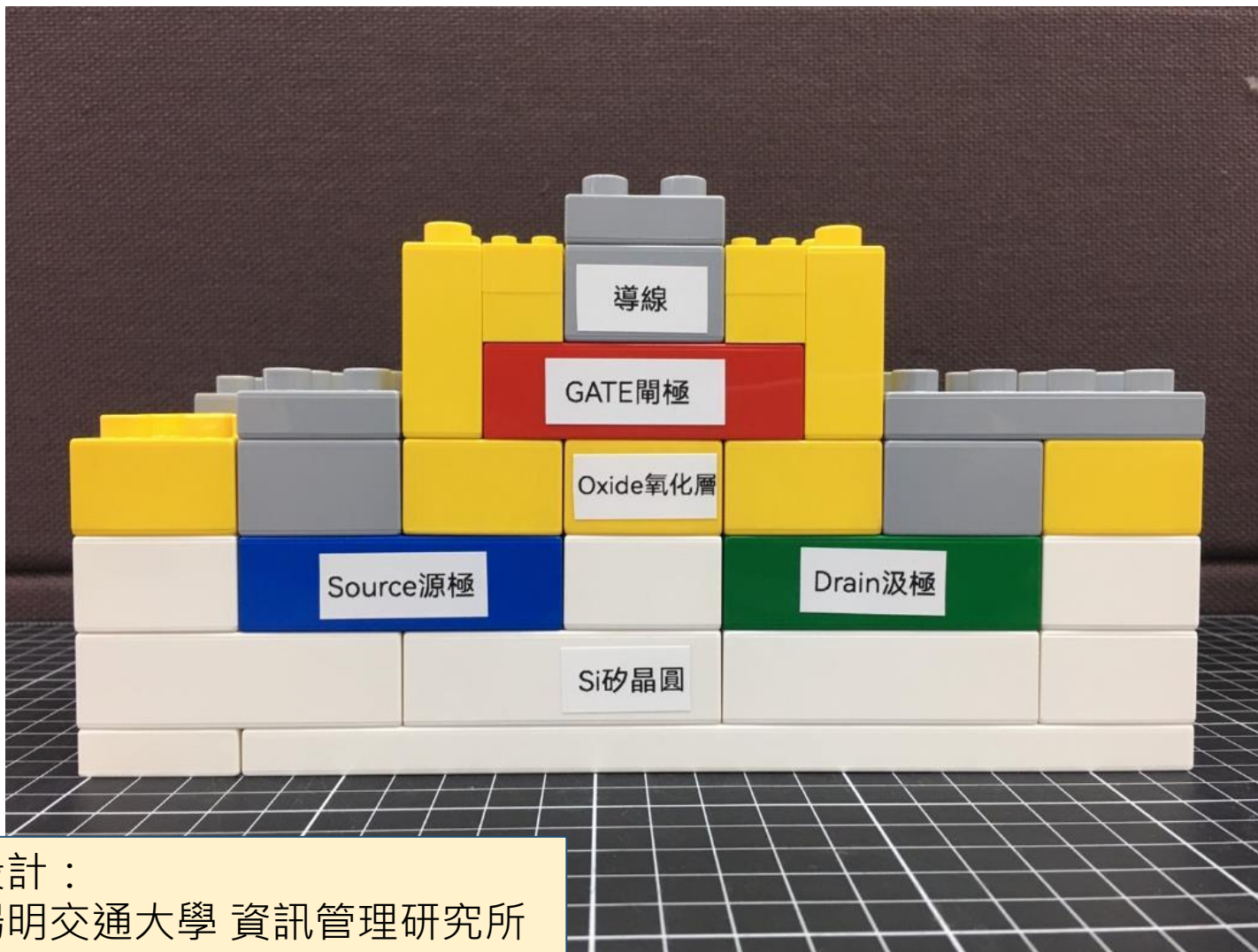


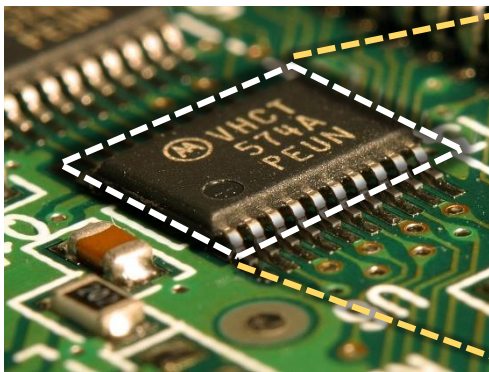
# 用樂高積木介紹半導體製程



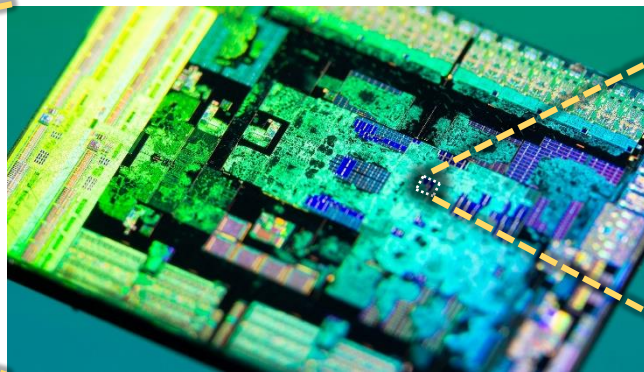
教材設計：  
國立陽明交通大學 資訊管理研究所  
研究生 林志威

# 電晶體簡介

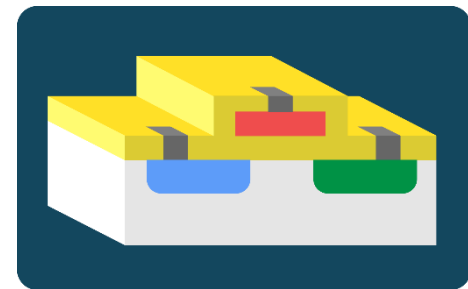
- 電晶體是積體電路(IC)等器件的基本組成單元。
- 電晶體有兩種最主要的作用，可以用來當作開關，也可以用來放大信號。
- 電晶體是用半導體材料(矽等)作出來的電子元件。
- 此講義以場效電晶體作為解說。



積體電路

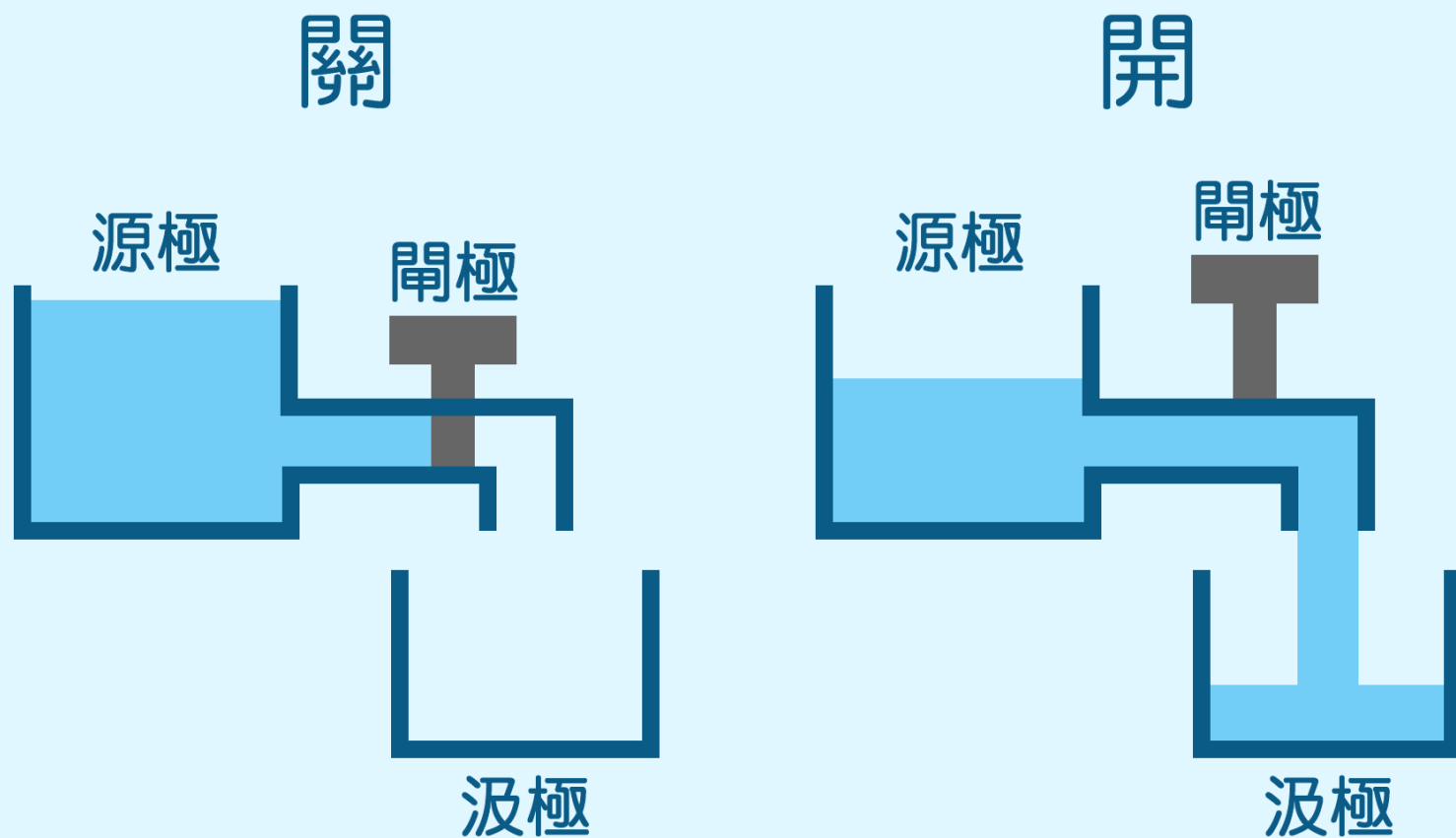


晶片



電晶體

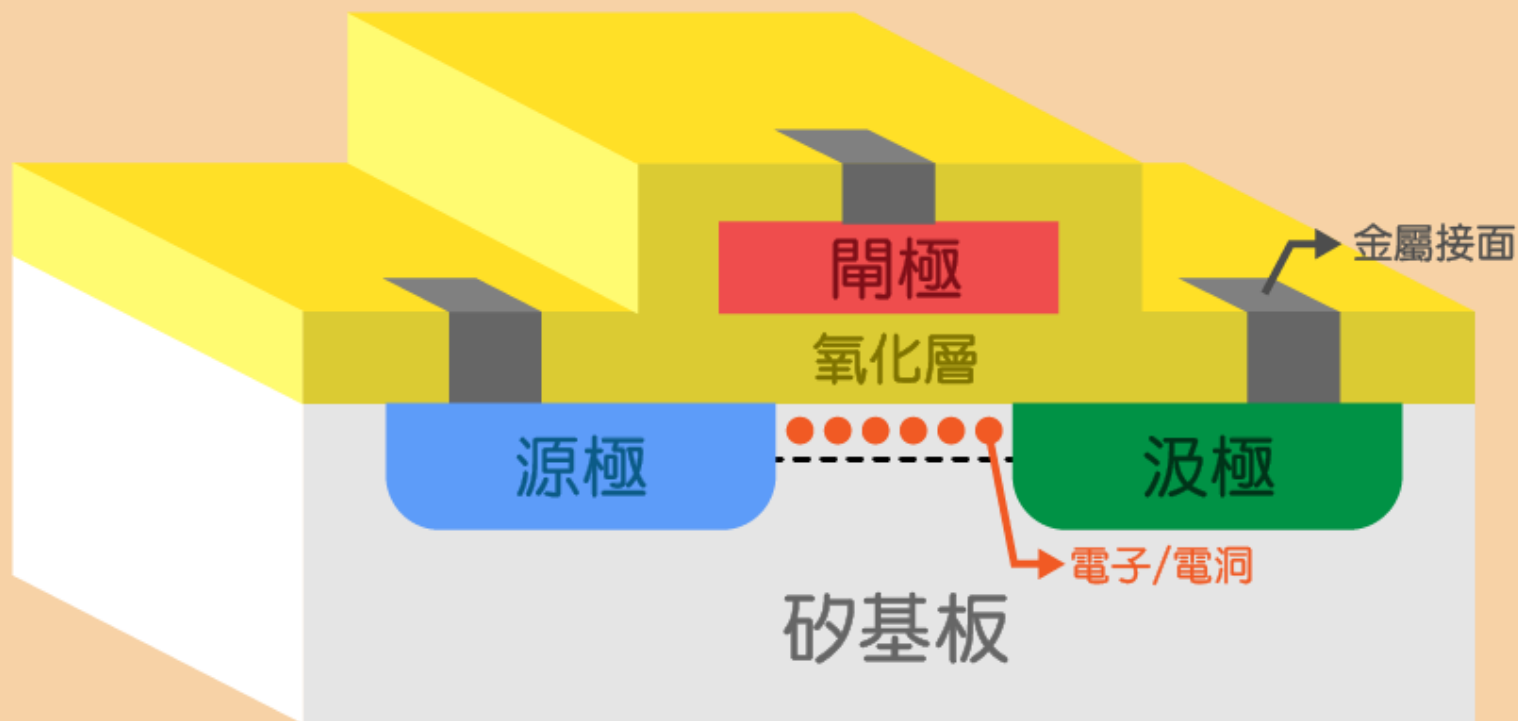
# 場效電晶體開關原理



製圖：林志威

# 場效電晶體

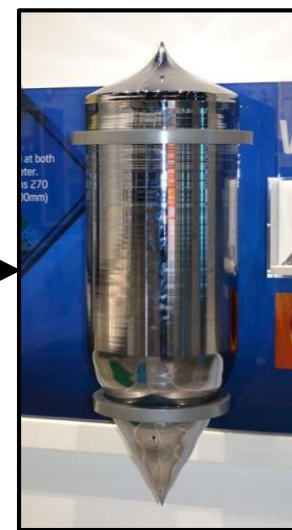
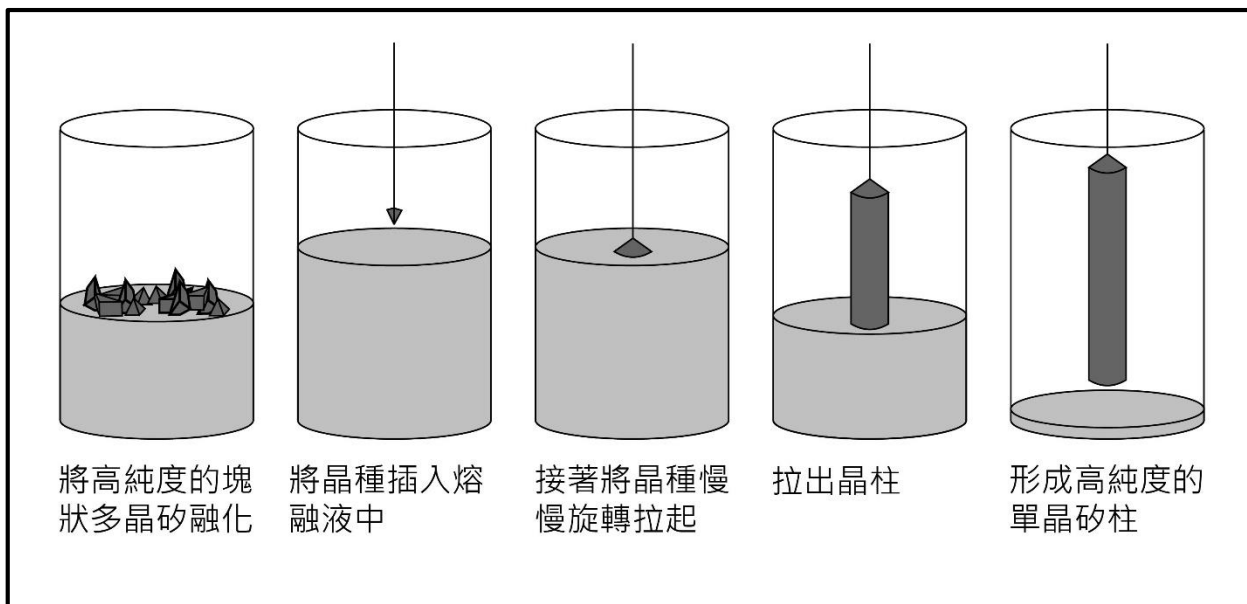
(Field-Effect Transistor, FET)



\*註：此為簡易版，省略基極

製圖：林志威

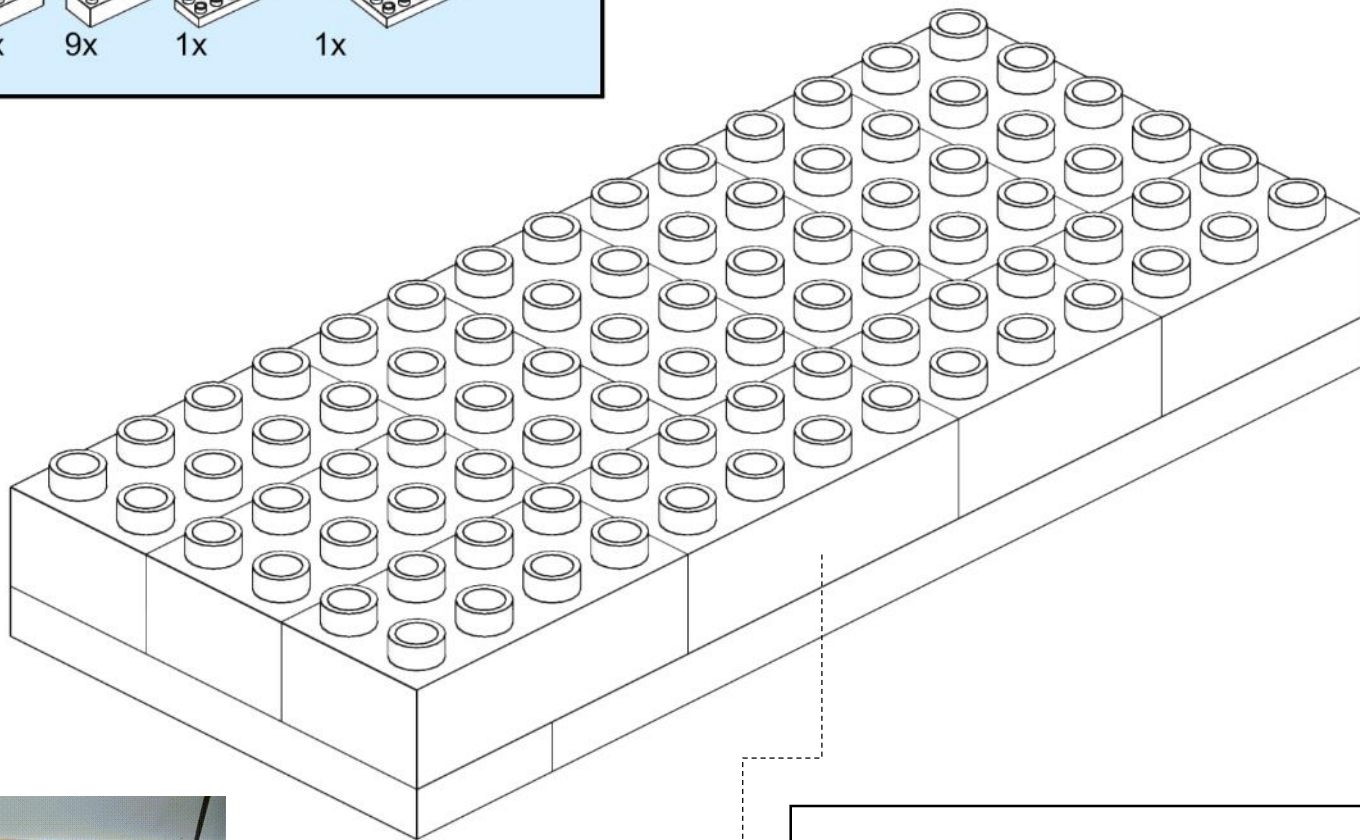
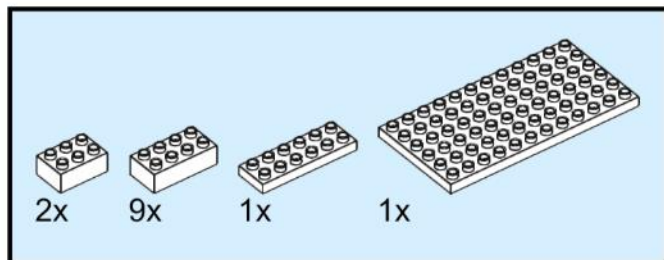
# 關於晶圓片的製作



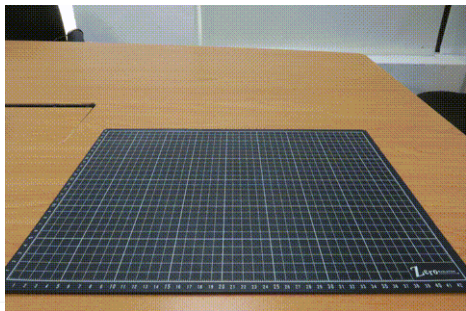
切割、拋光

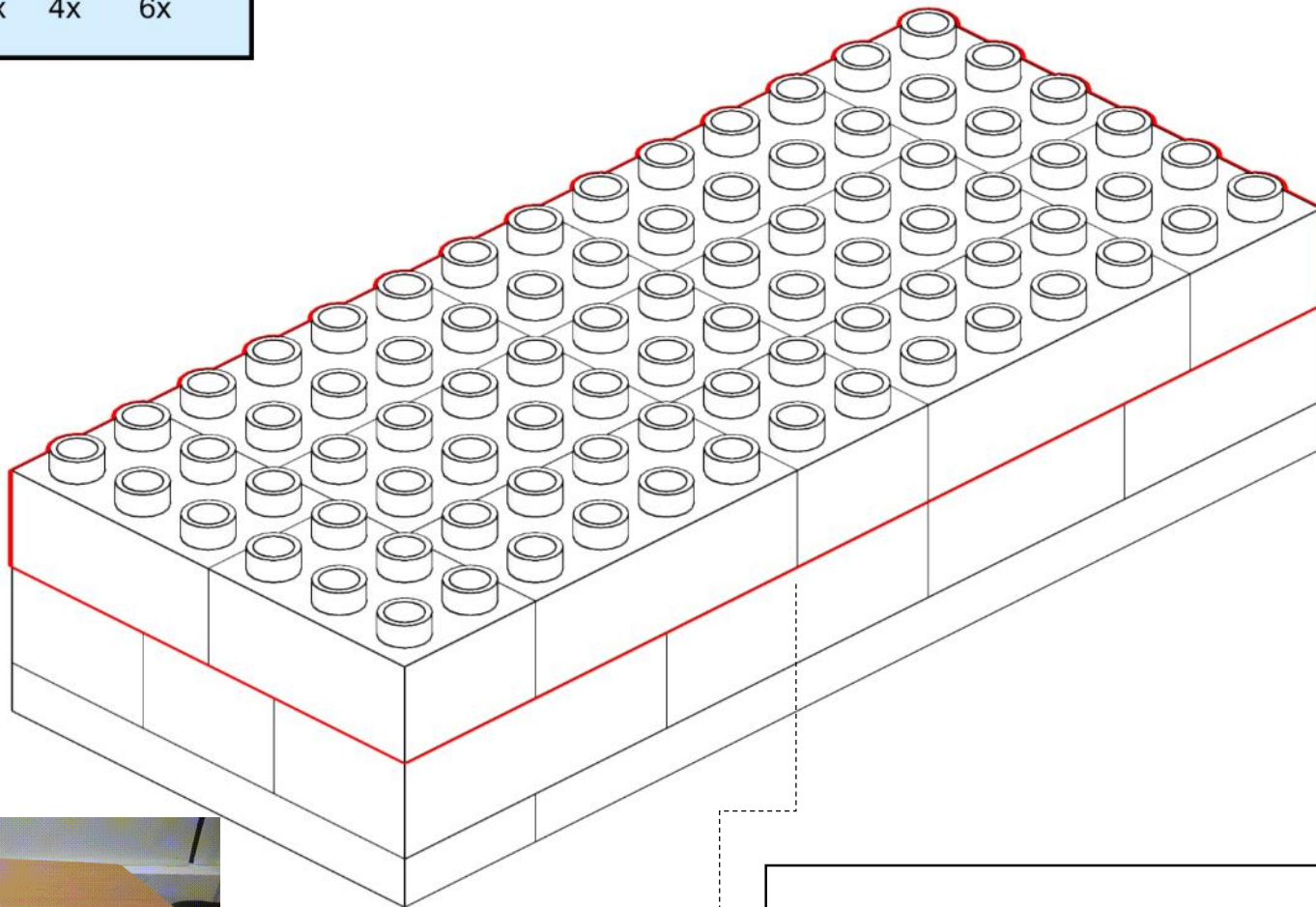
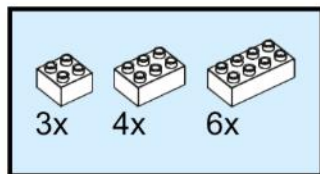


晶圓片

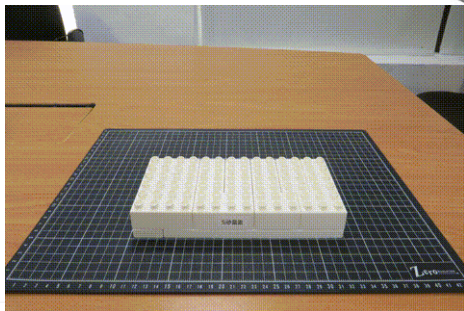


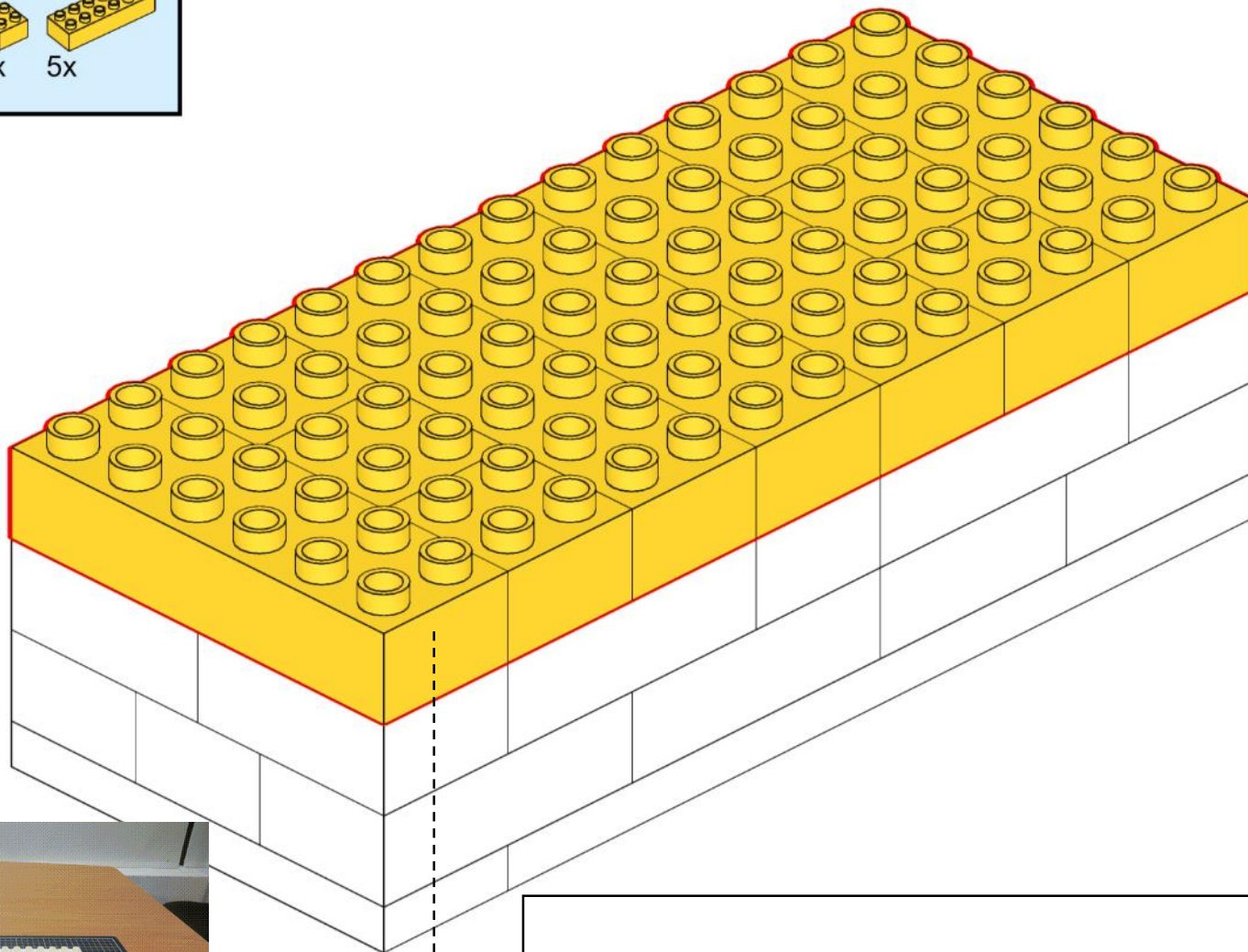
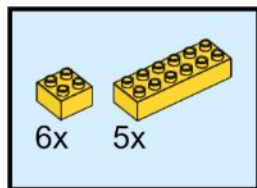
先拼一層白色積木



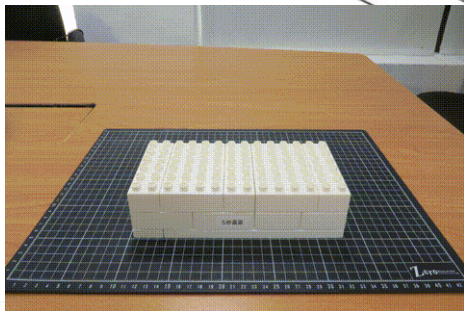


接著再一層白色積木。  
白色積木部分為矽晶圓。

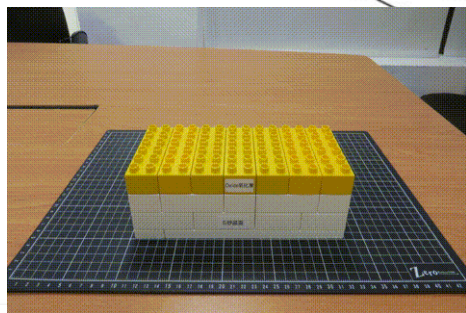
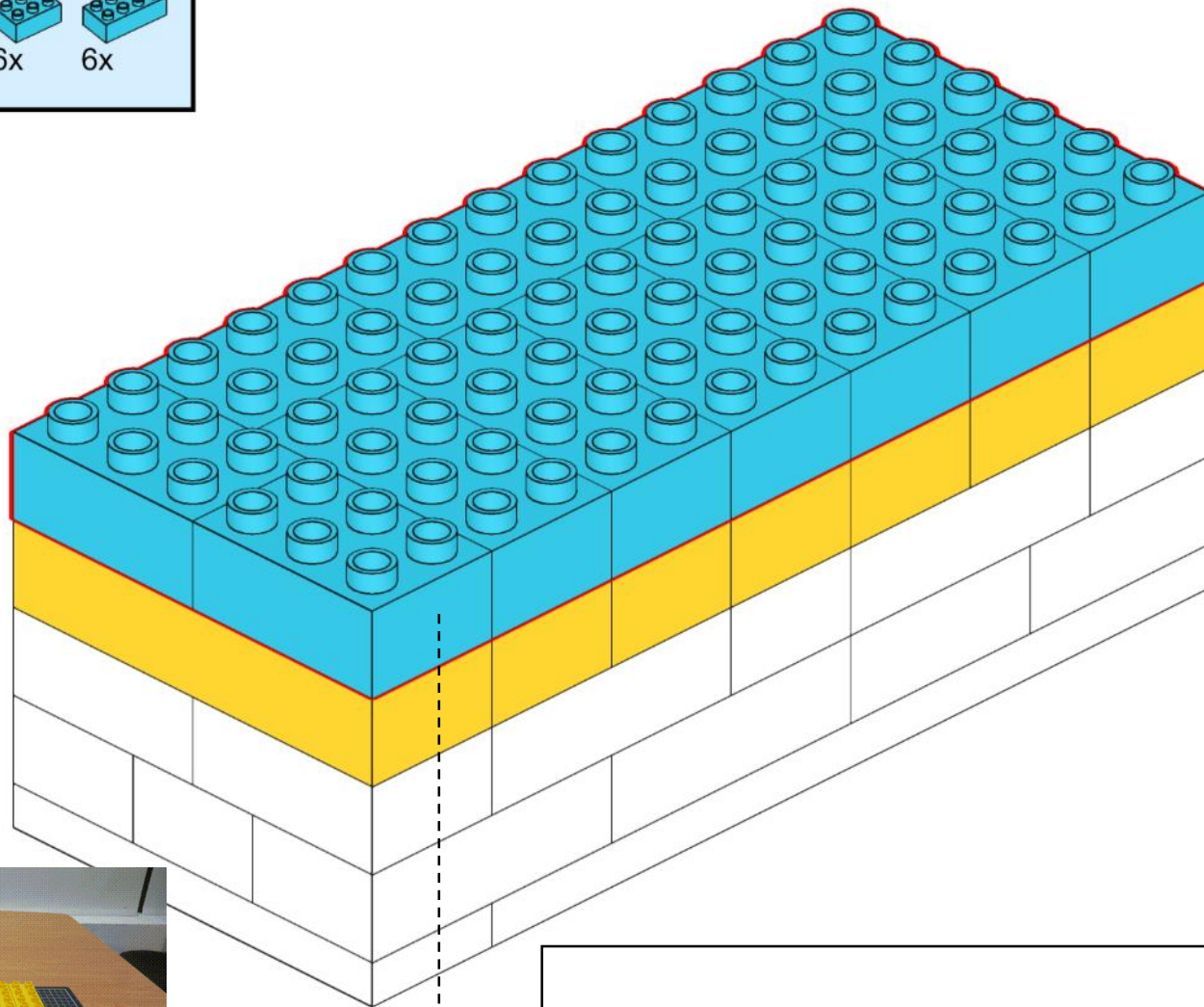
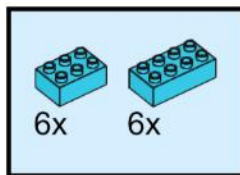




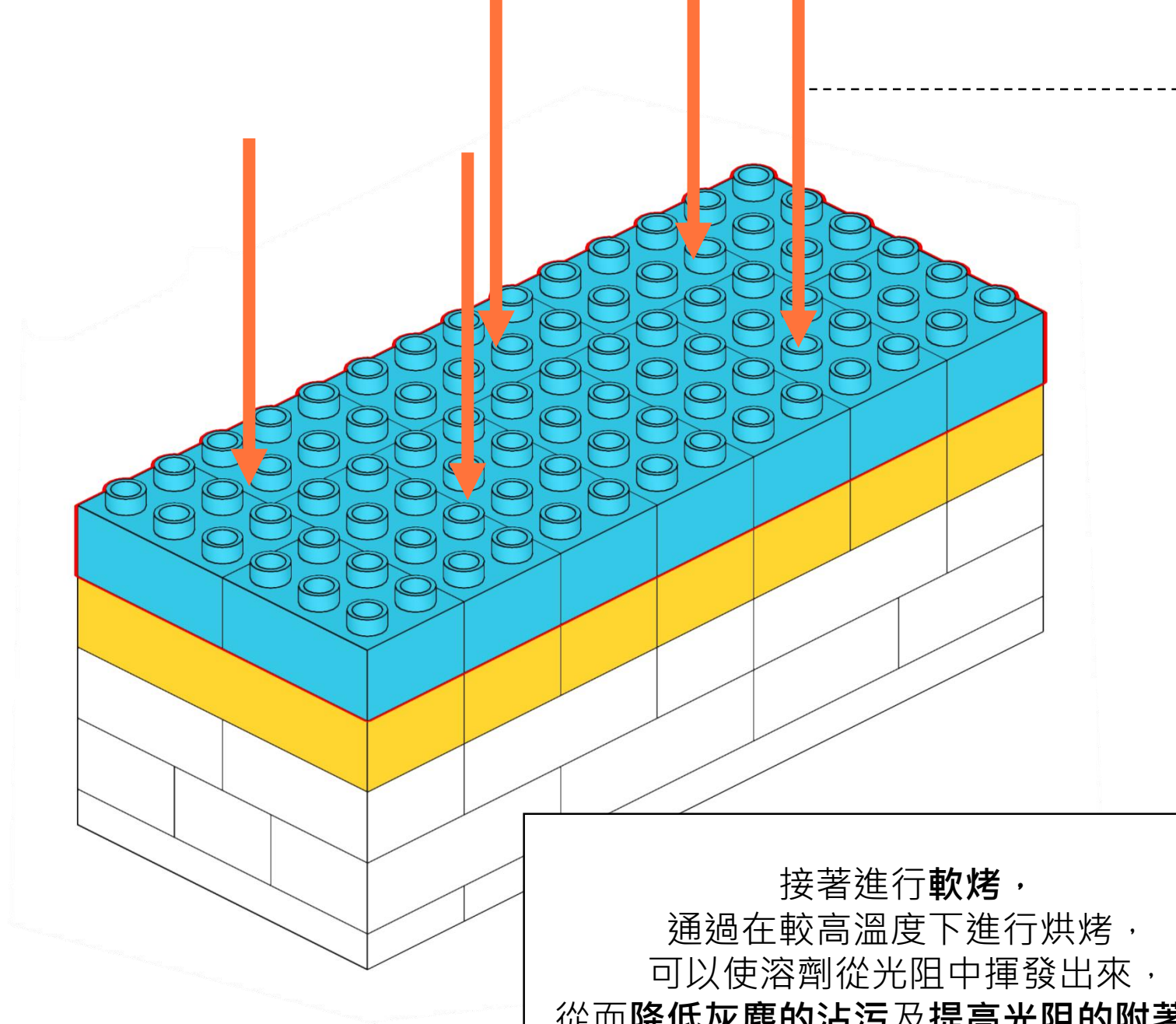
首先，會以高溫烘烤方式，  
在表面形成一層絕緣的氧化層(黃色積木)。







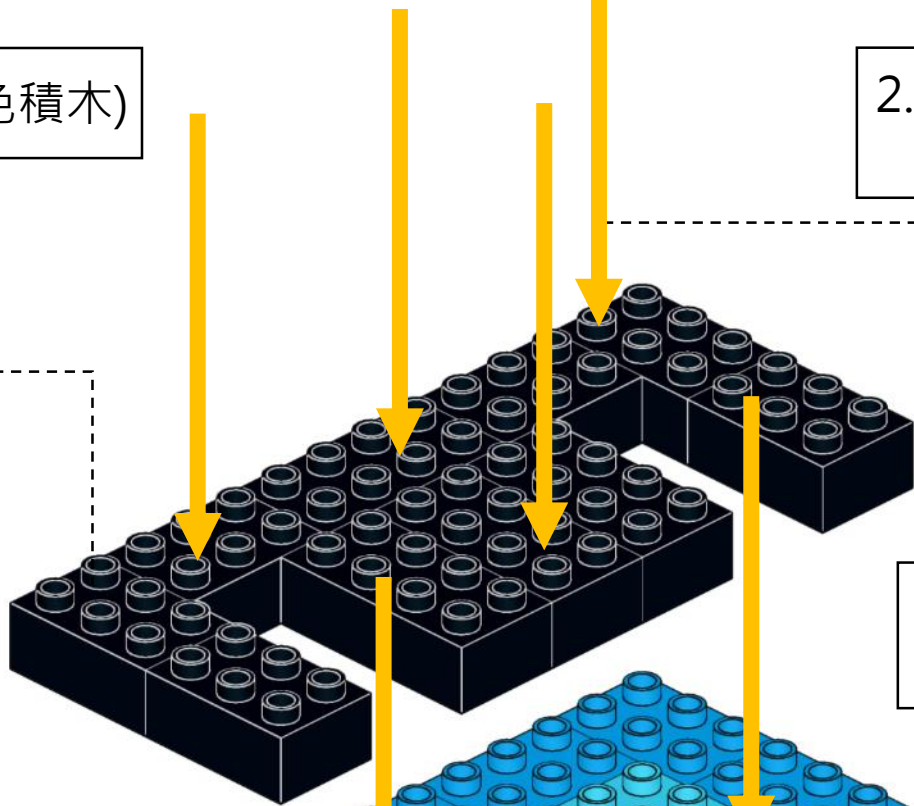
接著我們想將氧化層部分區域去除掉，  
先在氧化層上塗抹光阻劑(天藍色積木)。



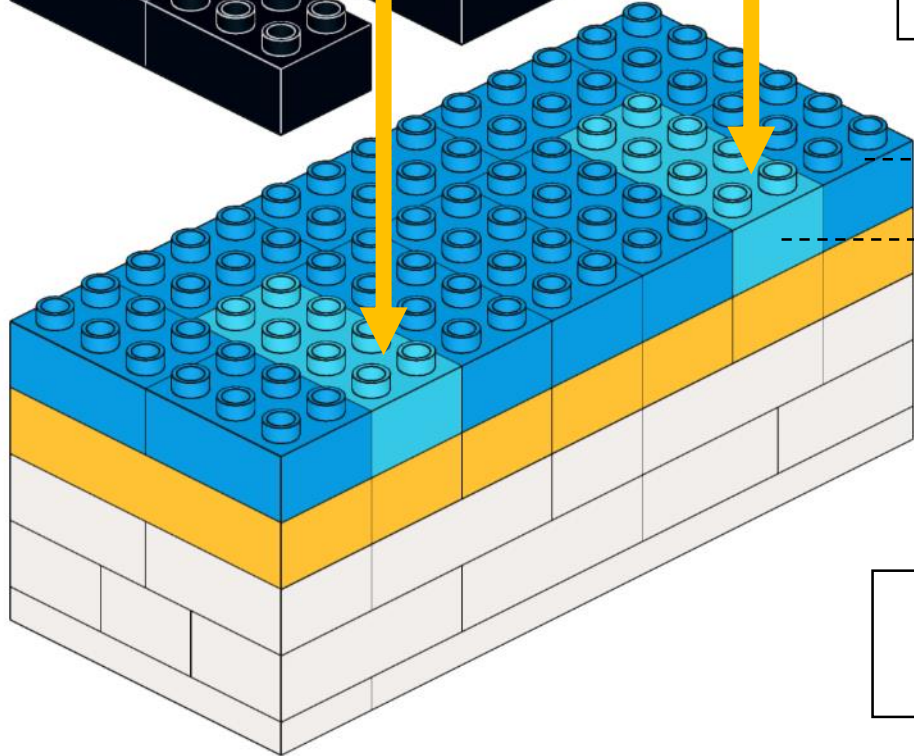
接著進行軟烤，  
通過在較高溫度下進行烘烤，  
可以使溶劑從光阻中揮發出來，  
從而降低灰塵的沾污及提高光阻的附著性。

1. 然後放上光罩(黑色積木)

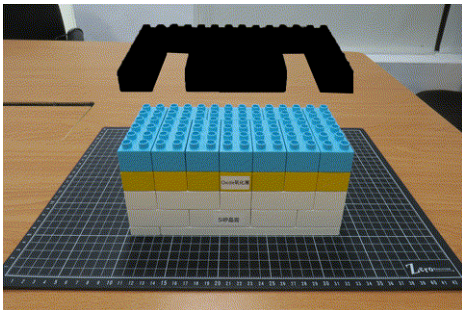
2. 進行曝光(黃色箭頭)  
通常為紫外光



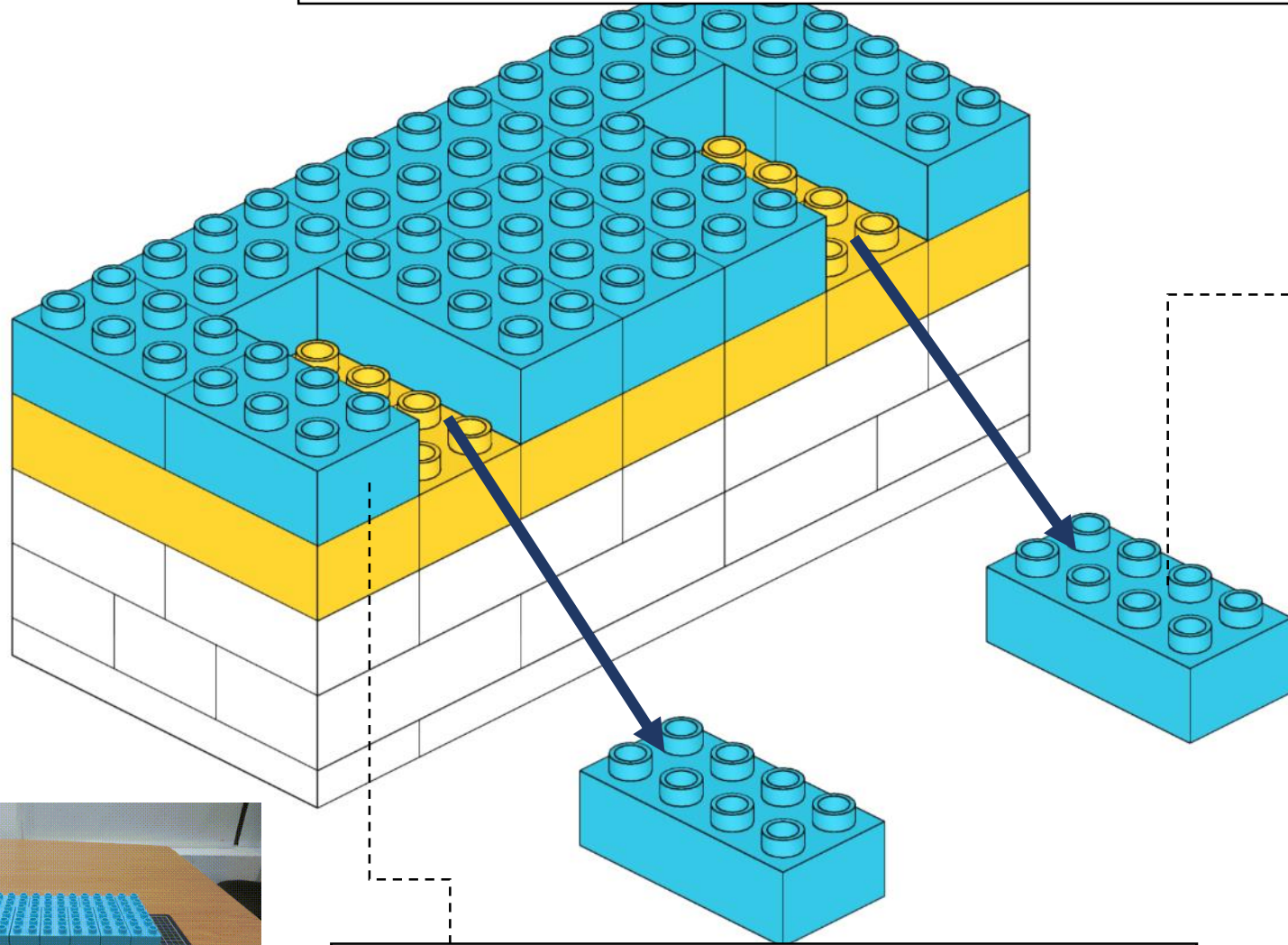
沒被照射到的地方  
(深天藍色積木)



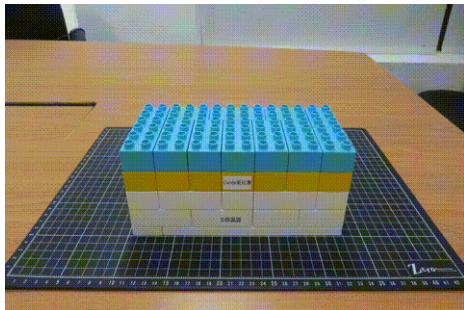
被照射到的地方  
(藍色積木)

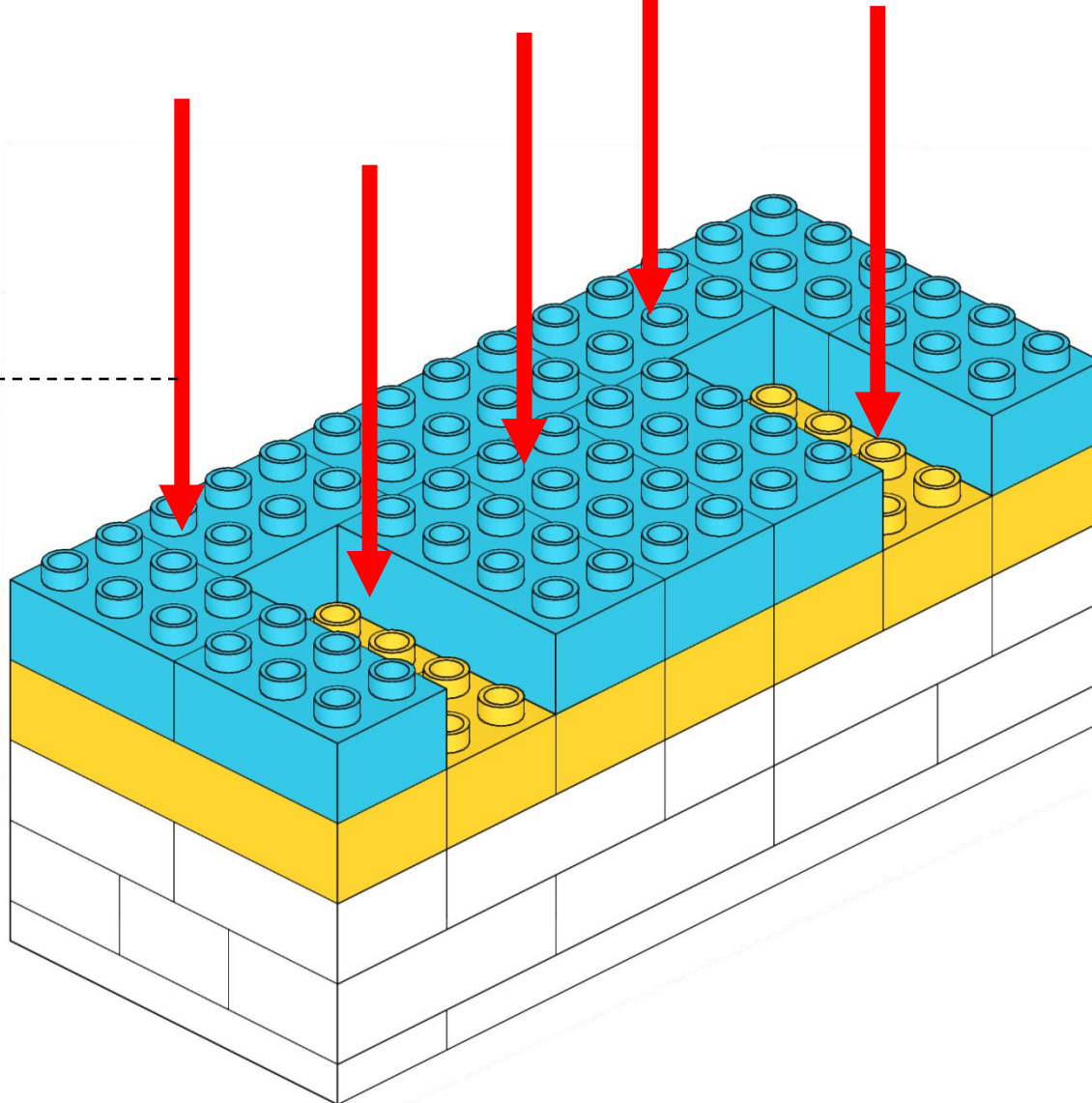


接著是顯影，  
剛剛被照射到的光阻劑，會因為當中的感光劑發生光化學反應，  
使光阻劑產生化學成分變化，並溶解於特定的顯影液。



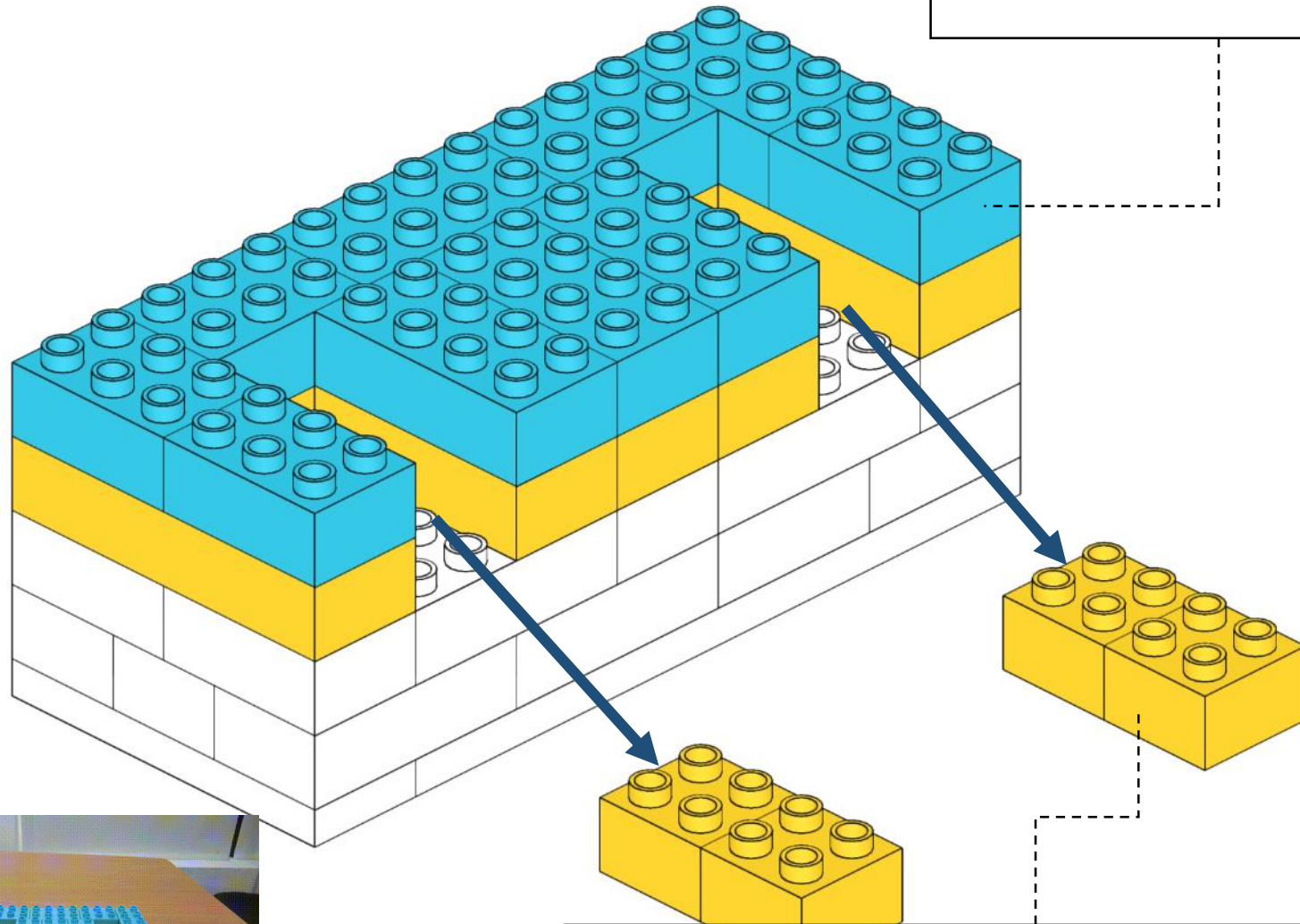
沒被照射到的光阻劑區域，  
則不會被顯影液溶解，所以會被保留下來。



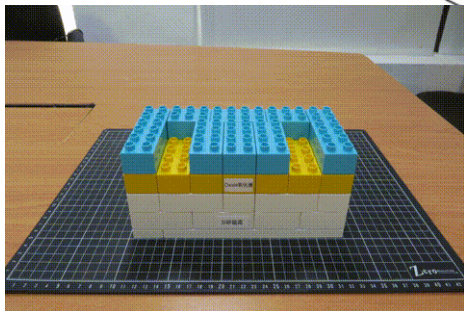


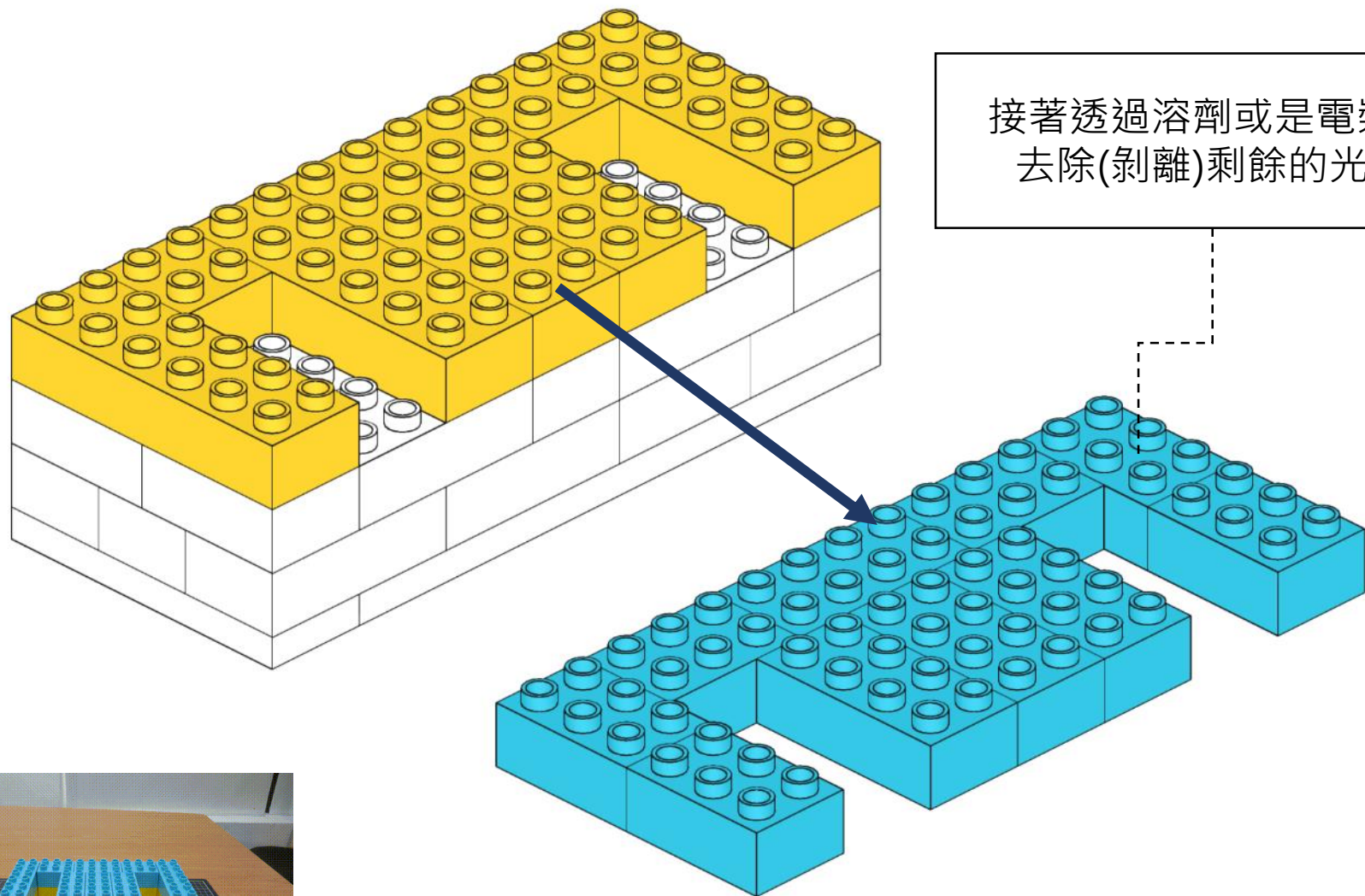
顯影後會進行**硬烤**，使光阻的性質更為穩定。  
在這過程中，利用高溫處理，  
提高光阻在隨後**蝕刻**和**摻雜**過程中的**抗蝕性能力**。

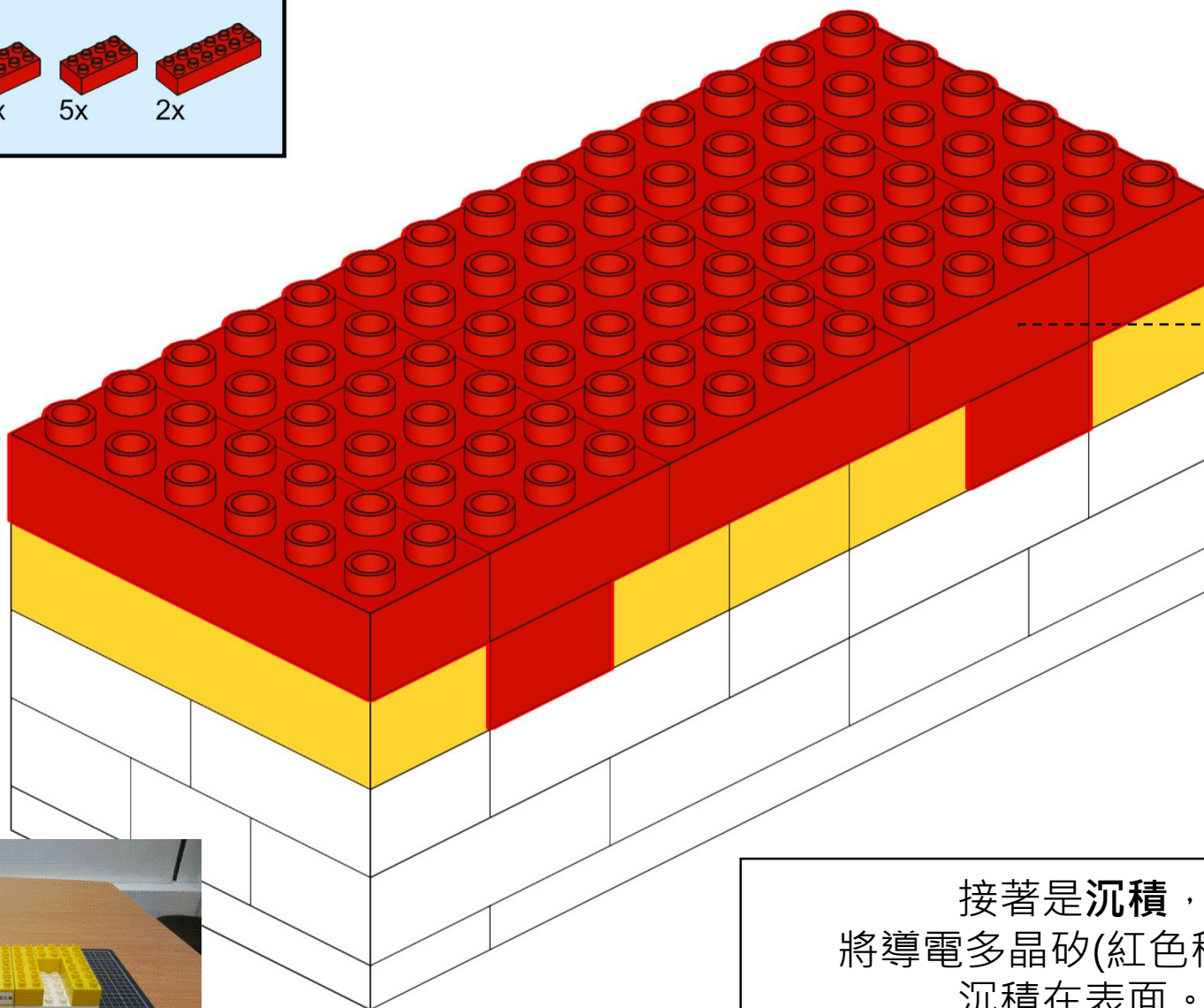
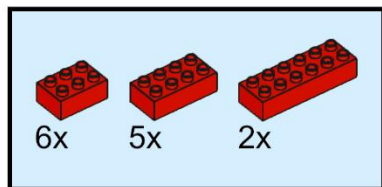
上層還有光阻的  
氧化層不會被蝕刻到。



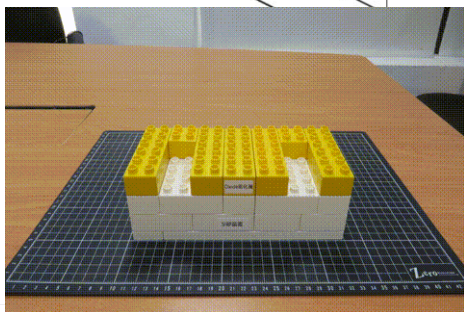
接著是蝕刻，  
蝕刻有分濕式蝕刻及乾式(電漿)蝕刻，  
都是利用化學反應的方式來削除下方的氧化層。



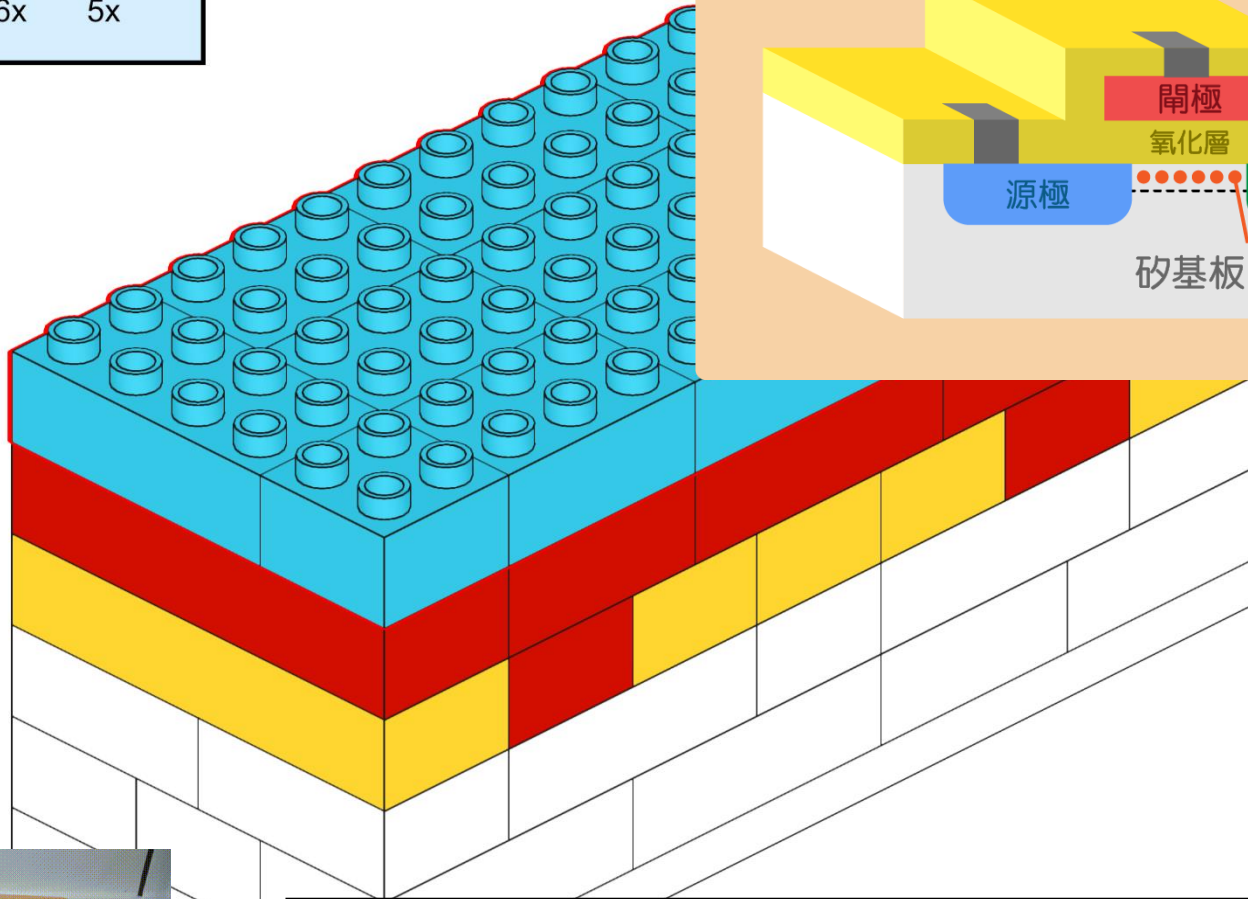
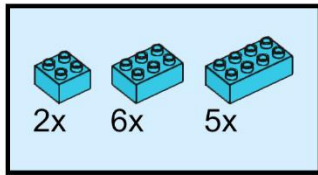




接著是沉積，  
將導電多晶矽(紅色積木)，  
沉積在表面。

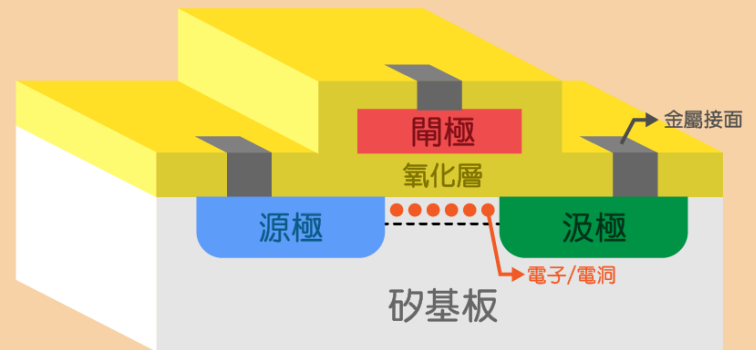




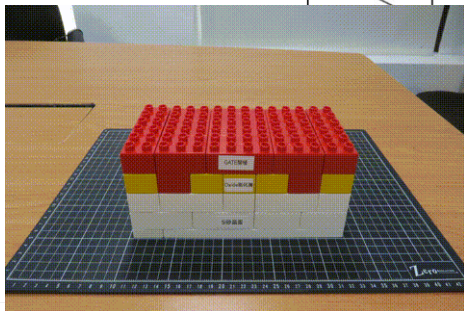


# 場效電晶體

(Field-Effect Transistor, FET)

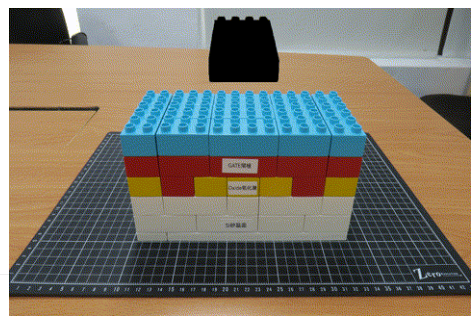
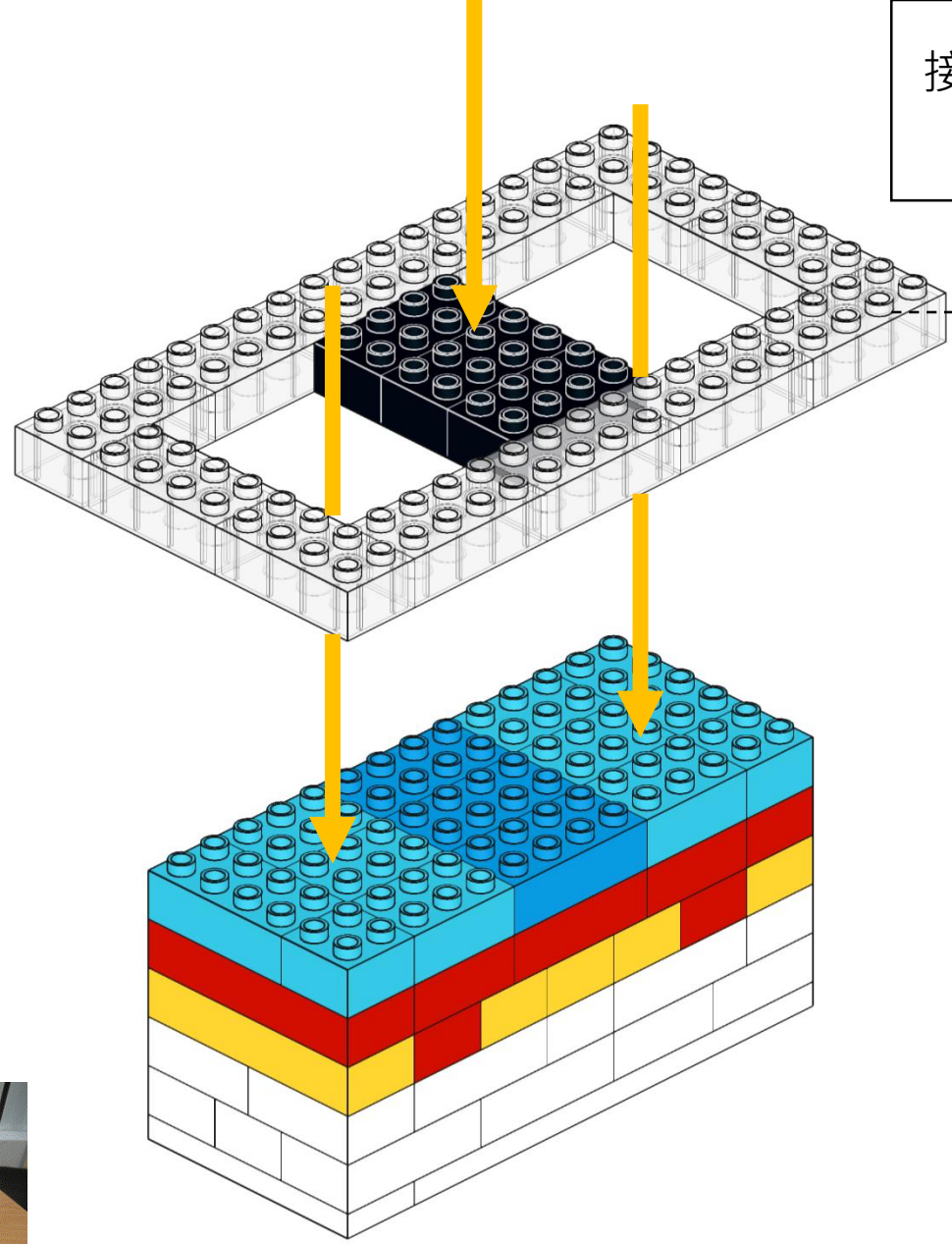


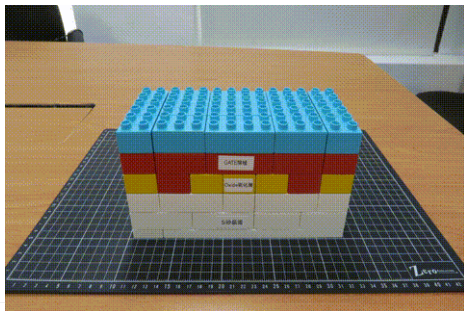
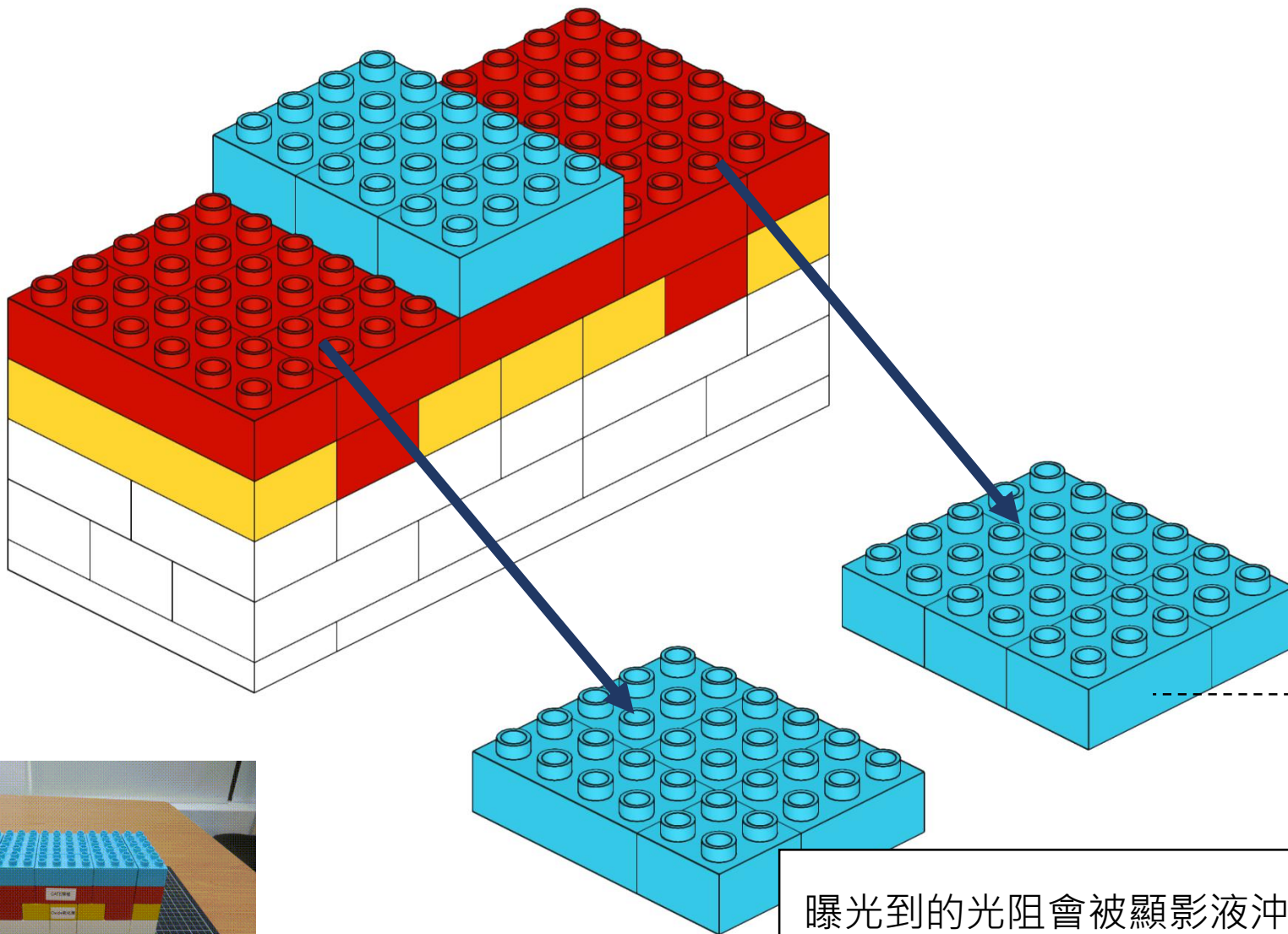
製圖：林志威



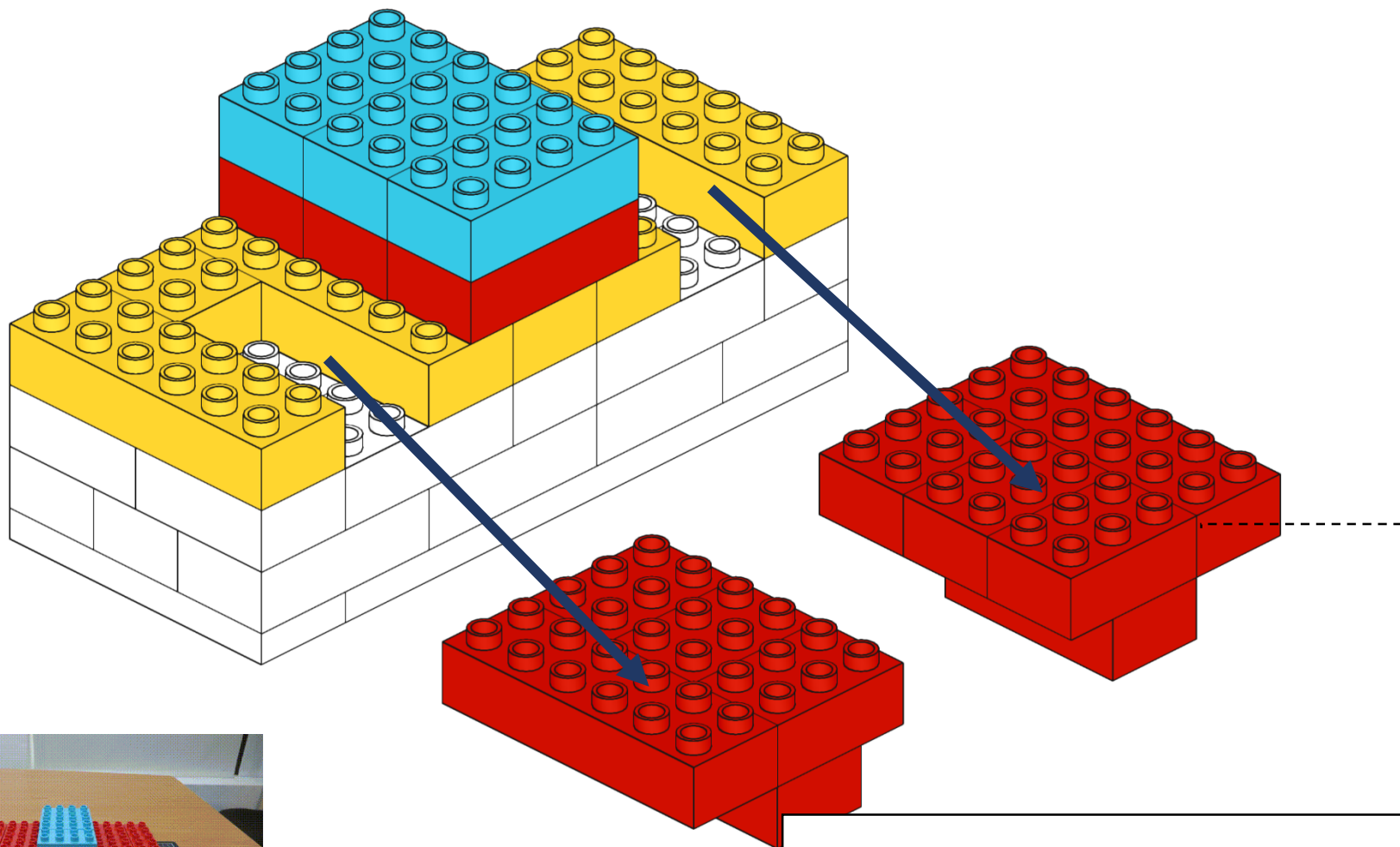
一樣塗抹光阻劑(天藍色積木)，並進軟烤。  
而我們只需要中間部分的導電多晶矽來做為閘極(Gate)，  
所以需要將旁邊多餘的部分去除。

接著一樣裝上光罩後，  
進行曝光。

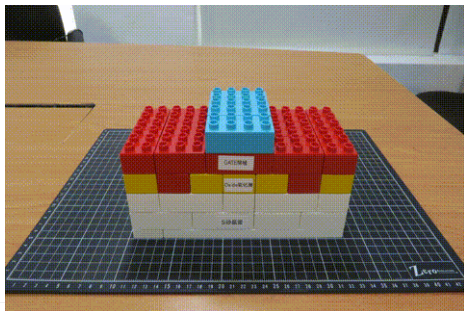


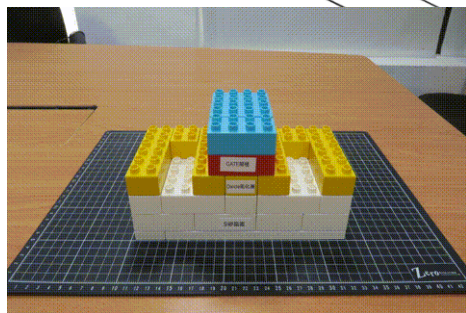
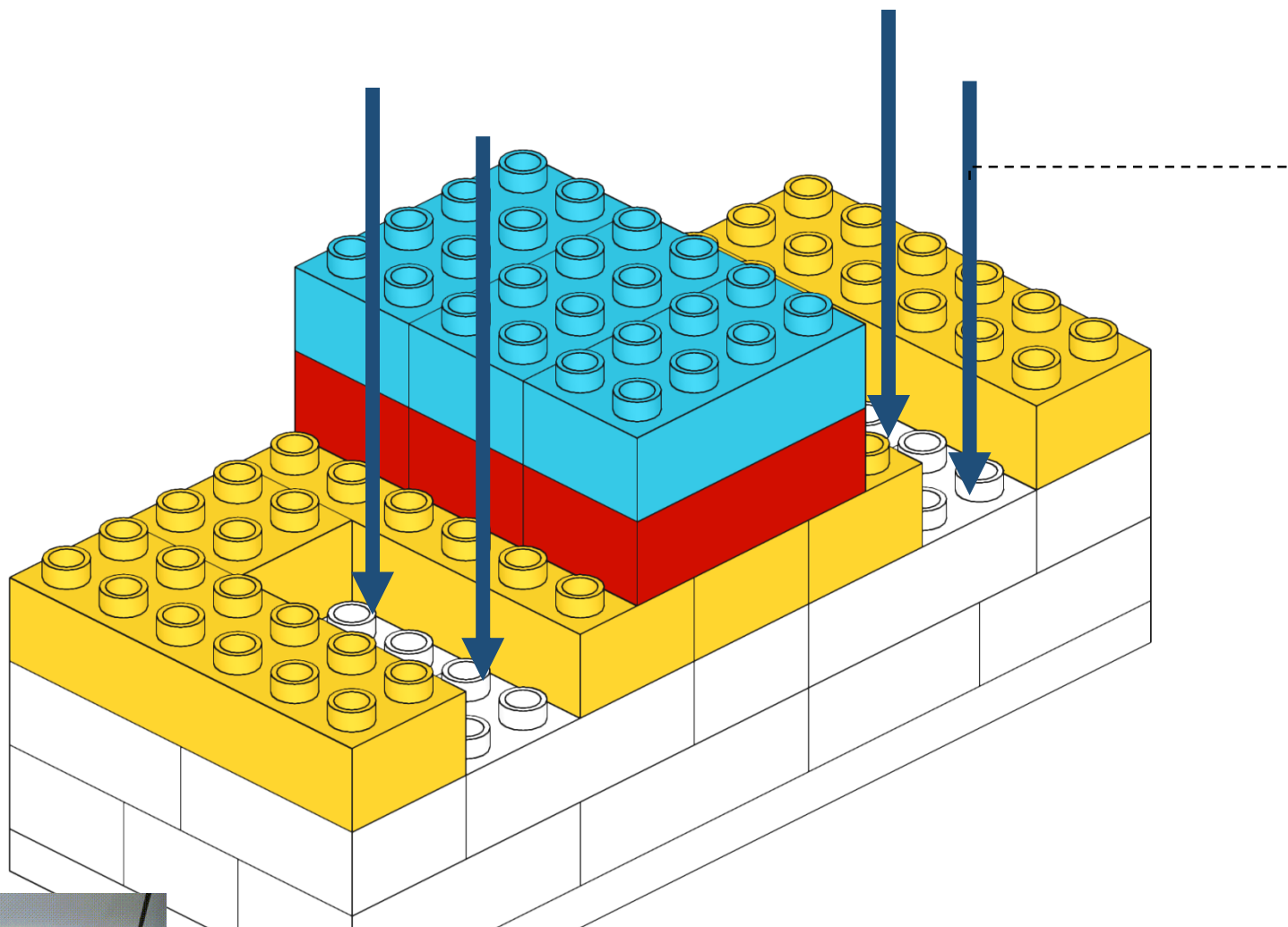


曝光到的光阻會被顯影液沖洗掉，  
並進行**硬烤**。



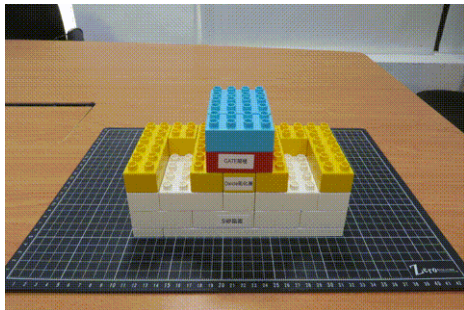
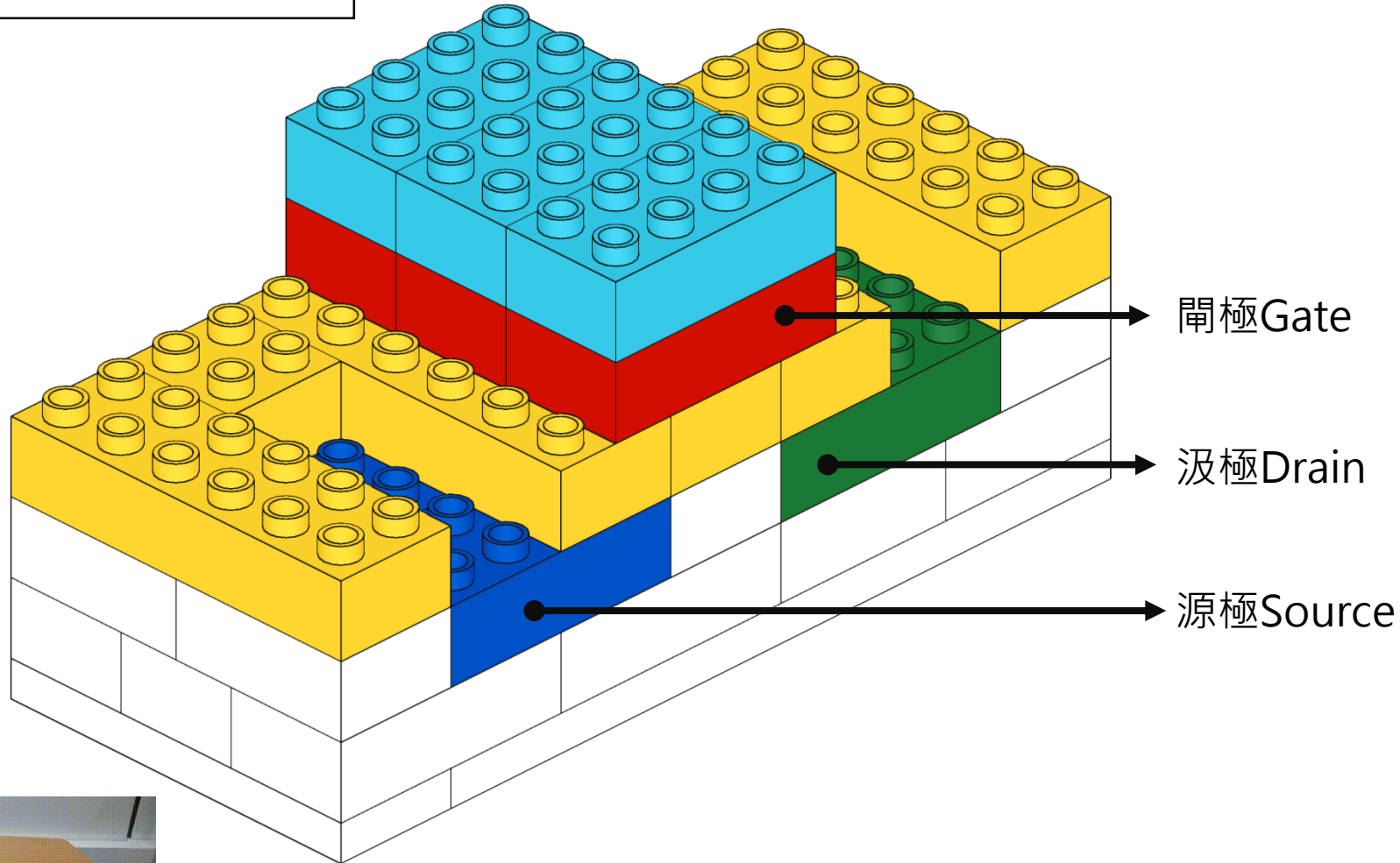
將旁邊的導電多晶矽蝕刻掉。  
而上層有光阻的會被保留下來。



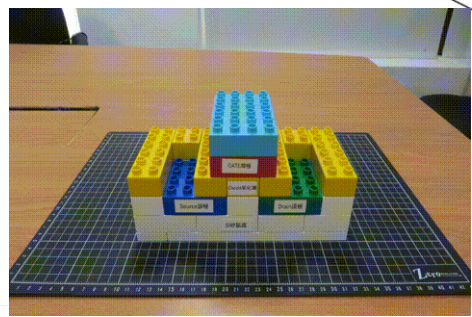
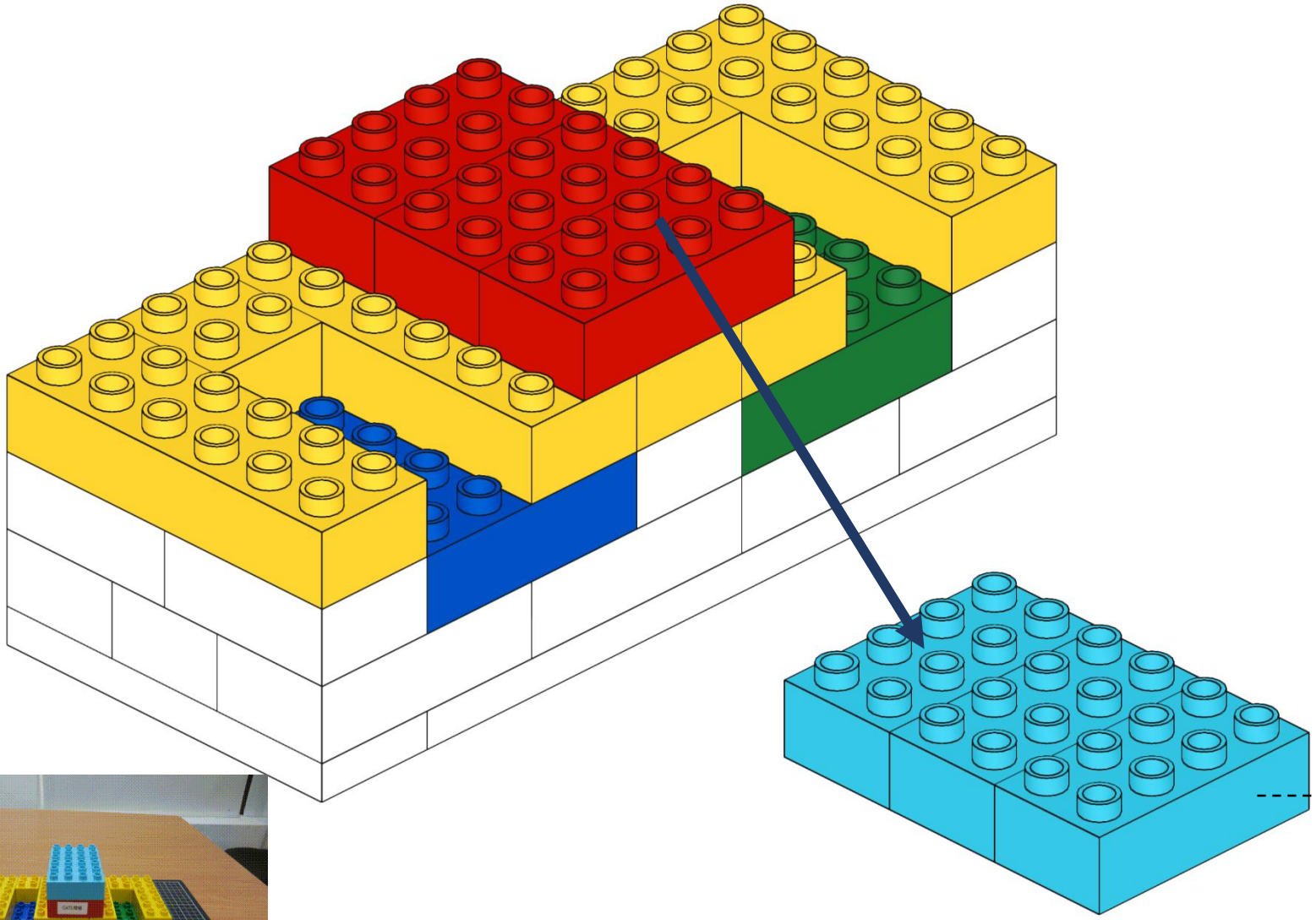


接著是**摻雜**，  
將硼或磷離子(電活性雜質原子，藍色箭頭)植入基底，  
使被植入的部分形成半導體元件。  
有離子植入法跟擴散法。

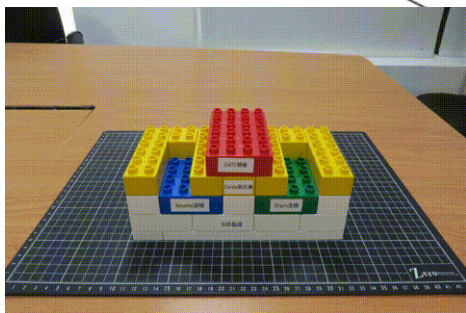
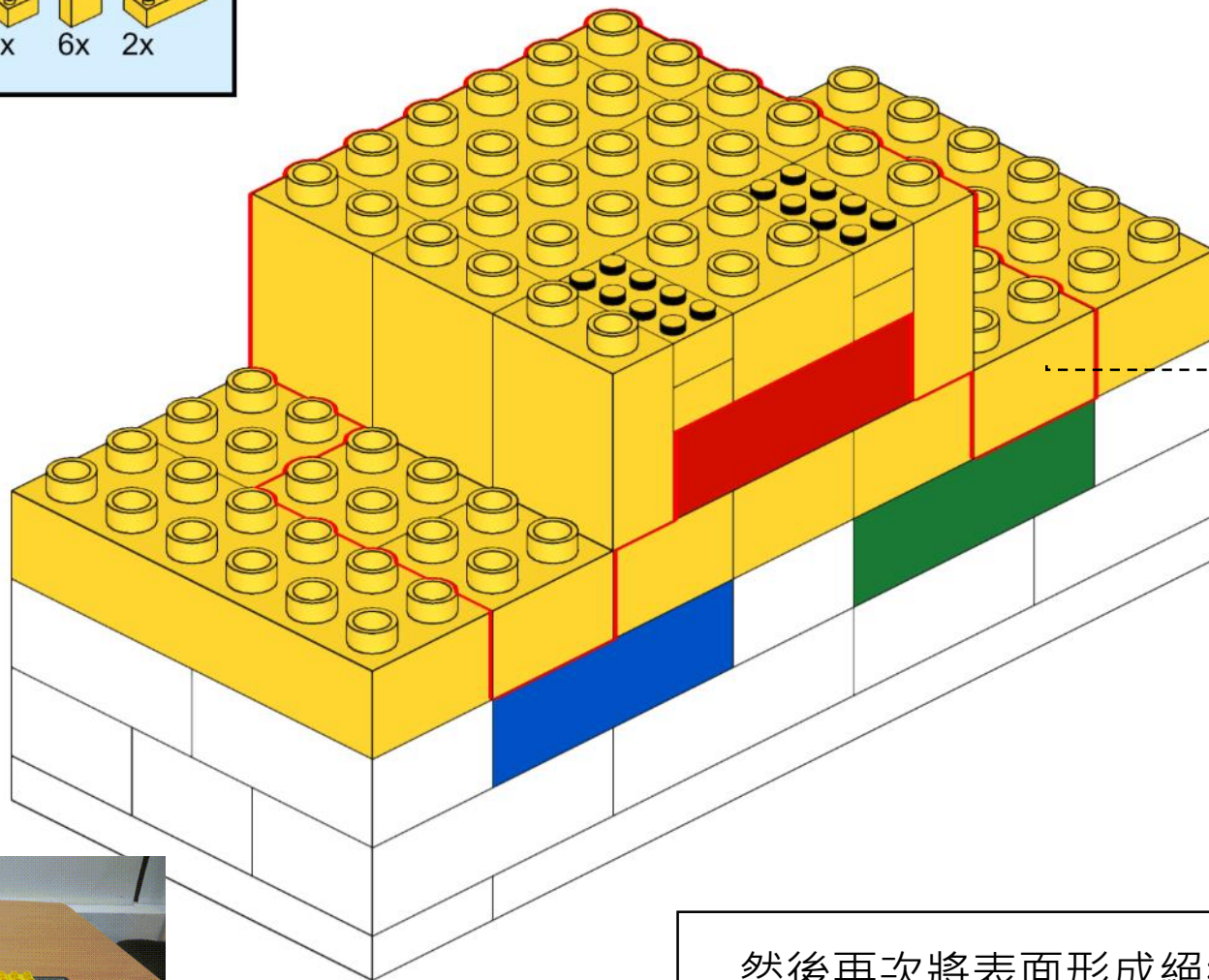
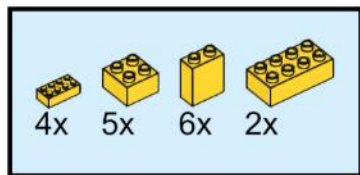
完成摻雜(擴散法)後的示意圖



完成後會有三個極性：  
閘極 ( Gate ) 、汲極 ( Drain ) 、源極 ( Source ) 。

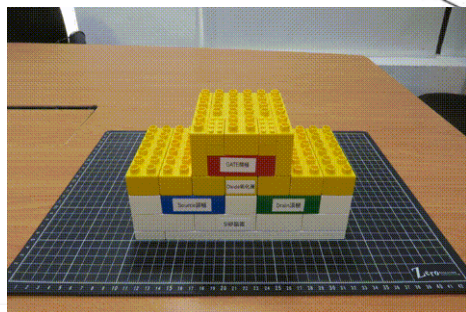
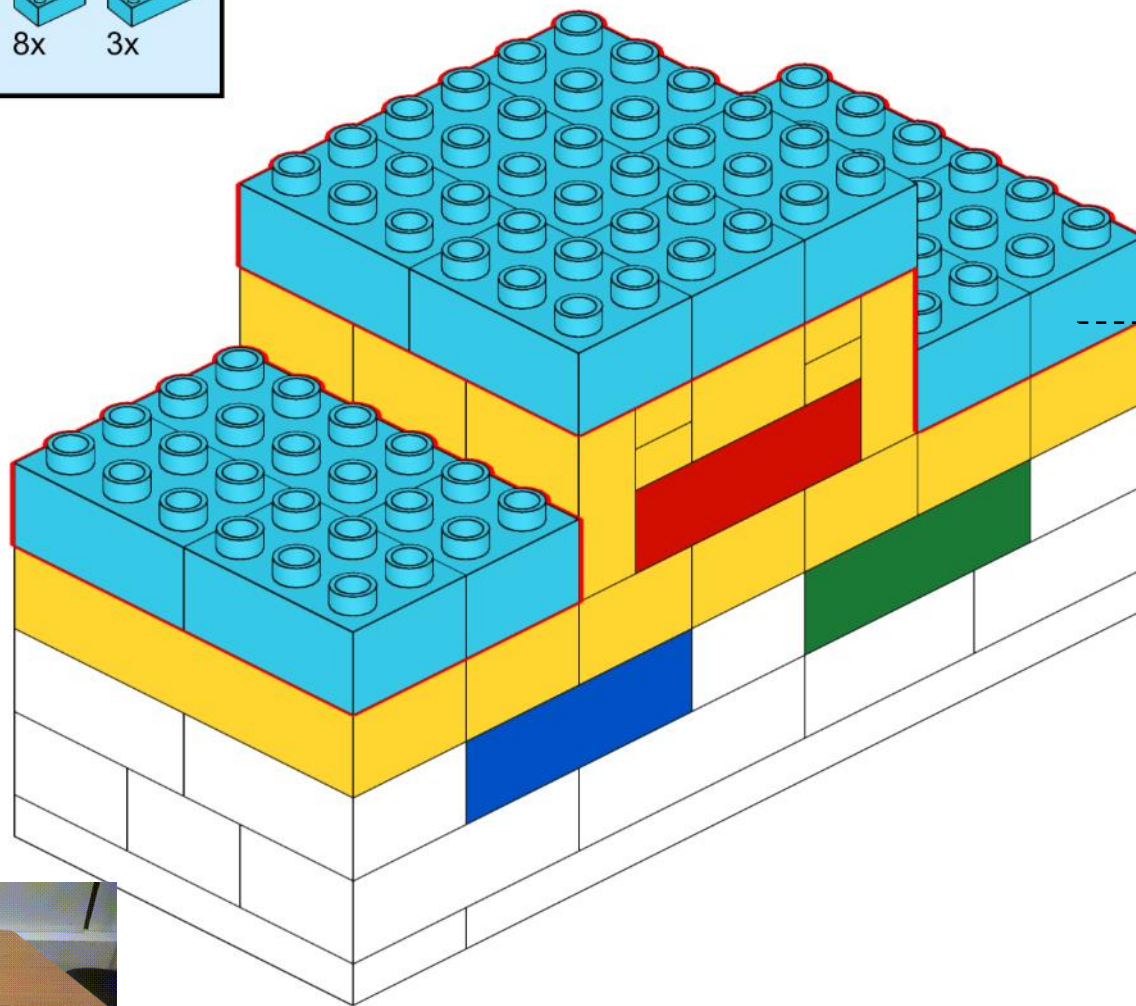
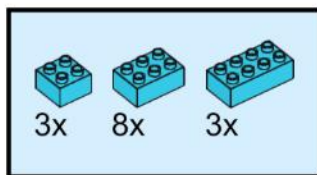


接著一樣把剩餘的光阻劑去除。

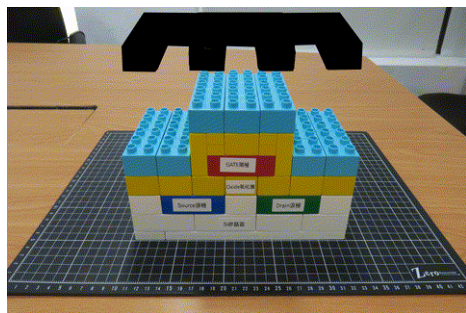
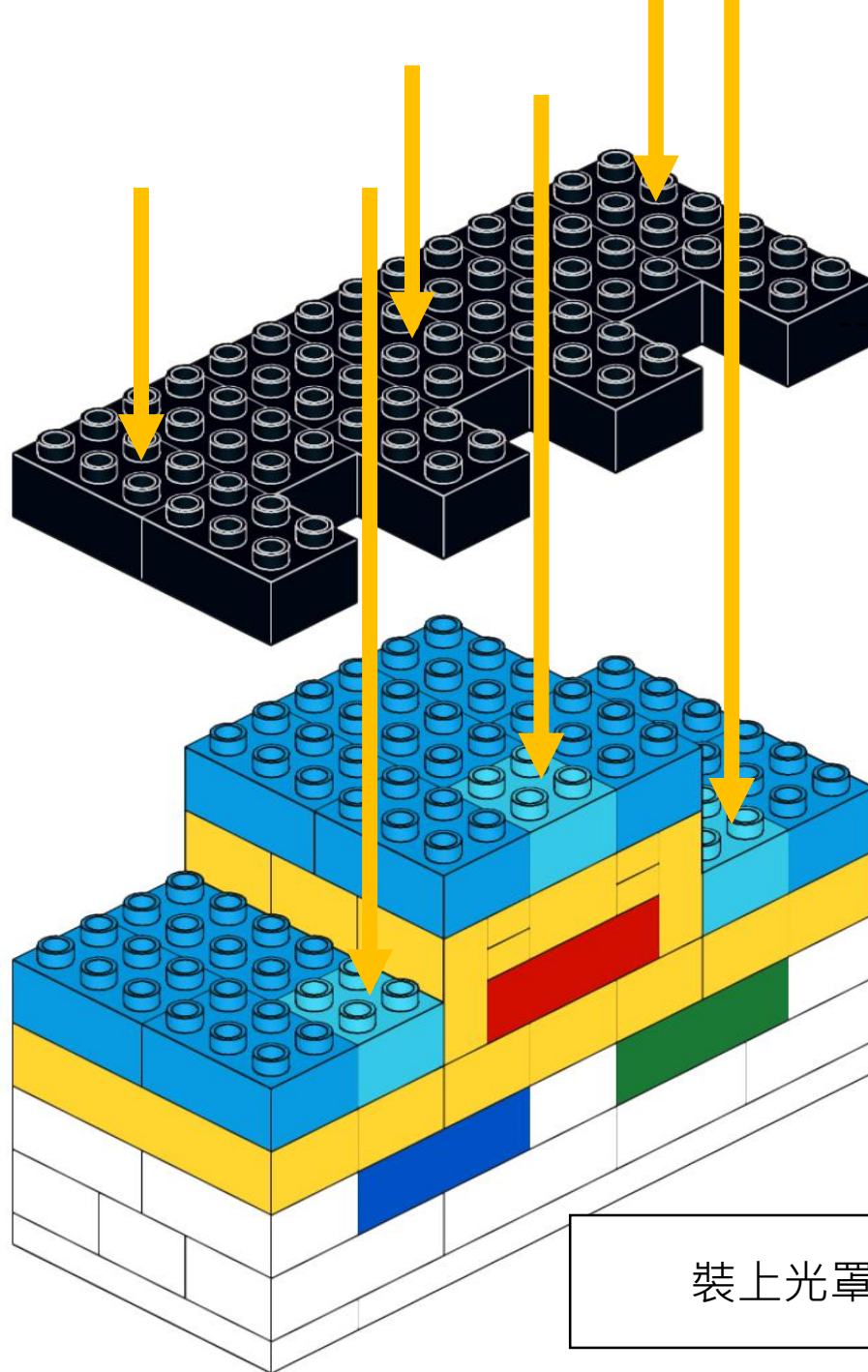


然後再次將表面形成絕緣氧化層。  
接著要在三個極上面開井窗，  
讓金屬導線可以接入。

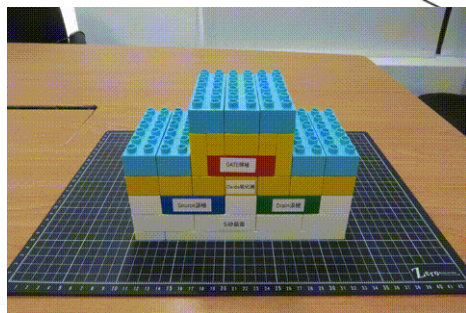
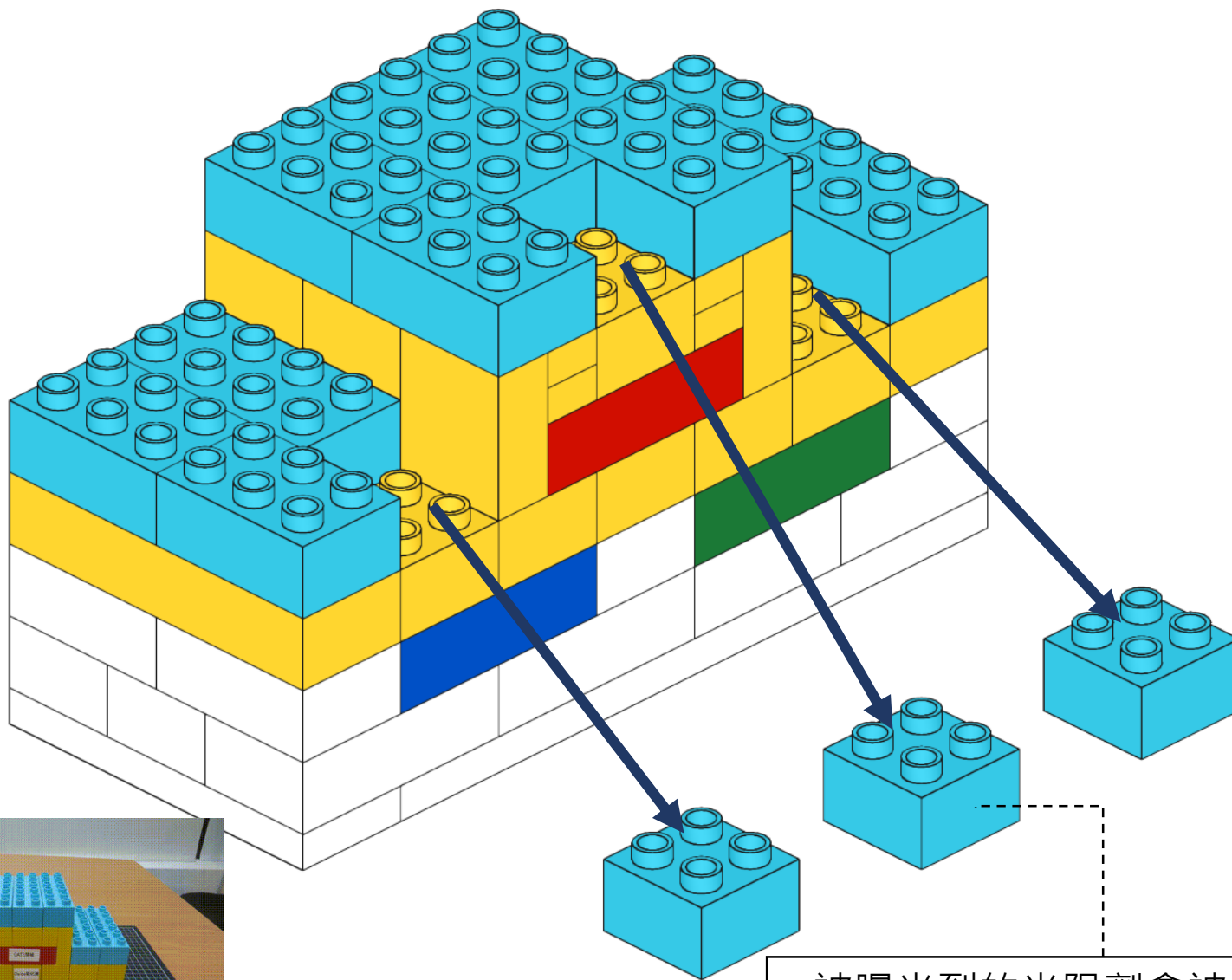




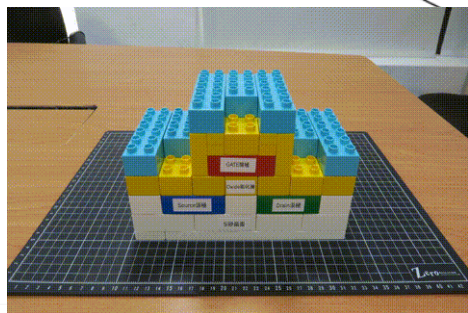
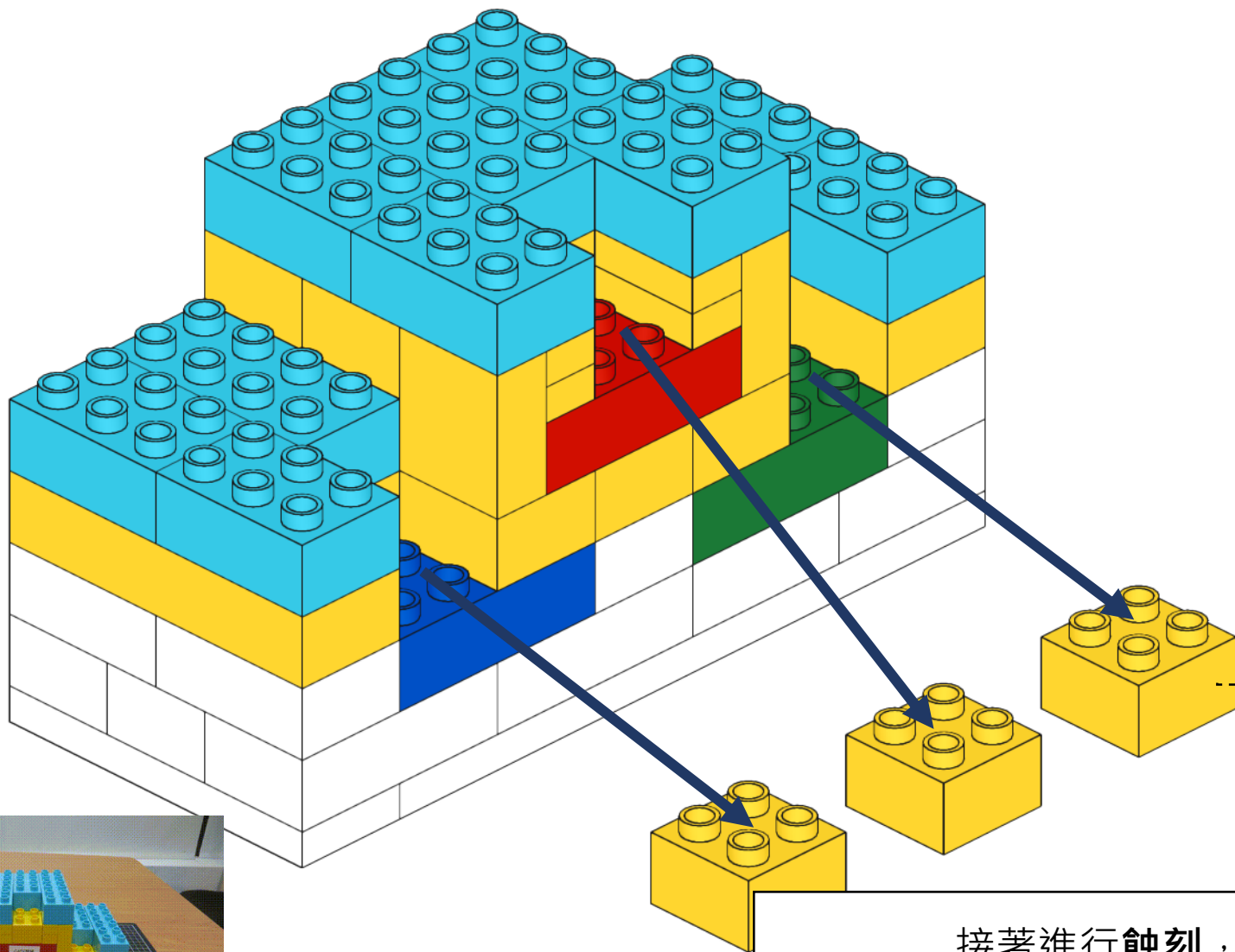
一樣塗抹光阻劑，並**軟烤**。  
以利在這三個極上各開一個洞(通道)，



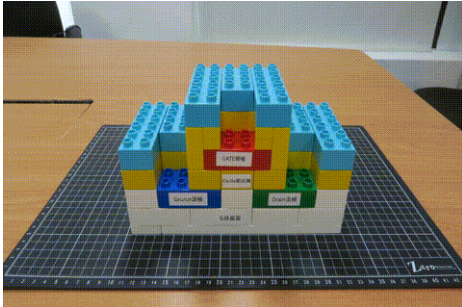
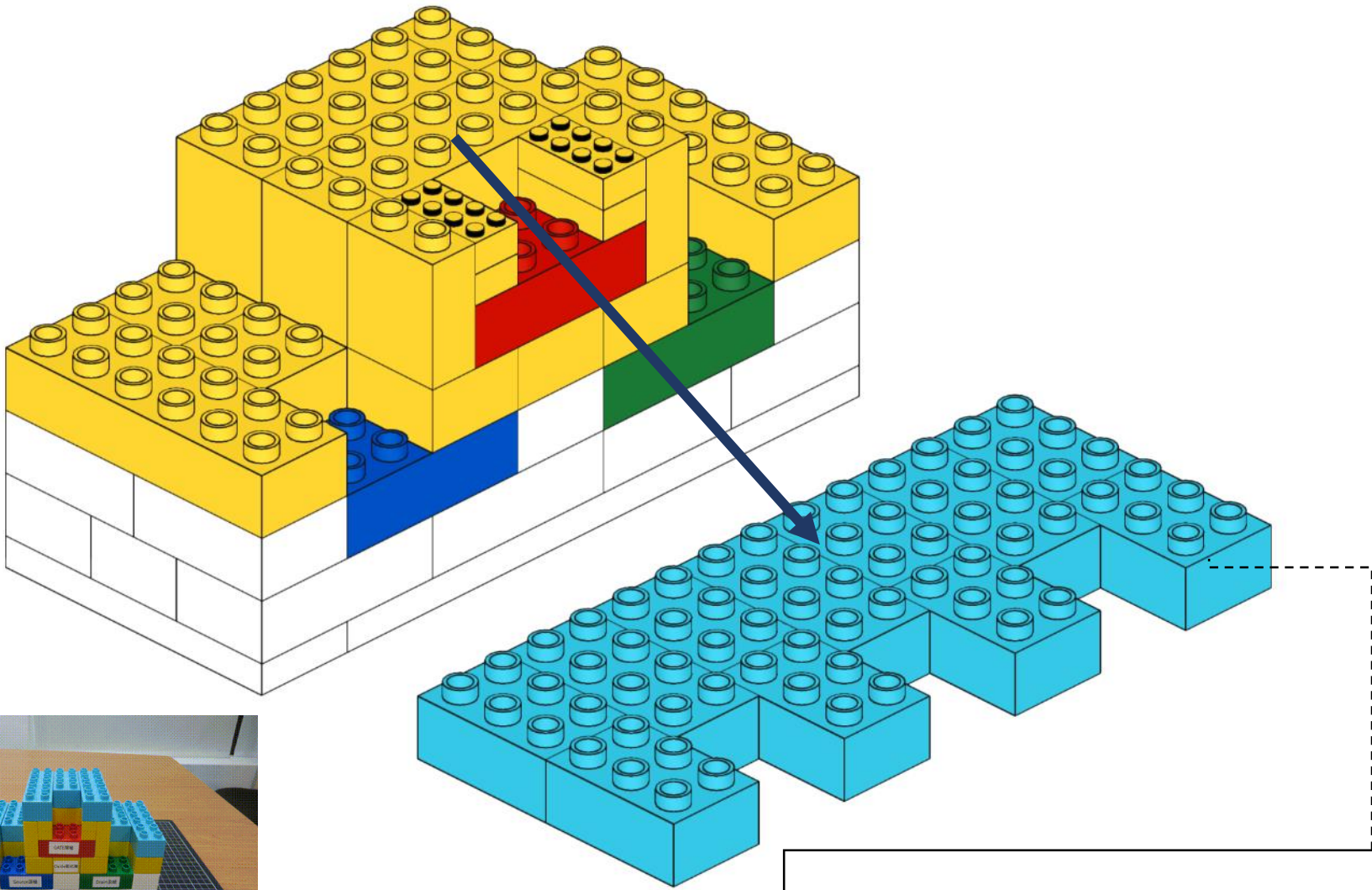
裝上光罩後，進行**曝光**。



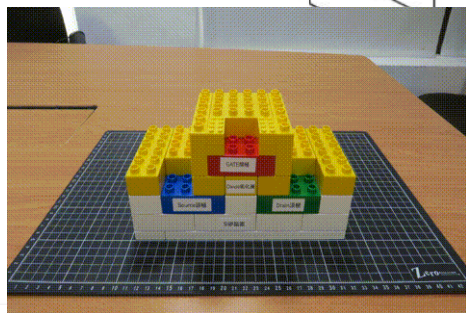
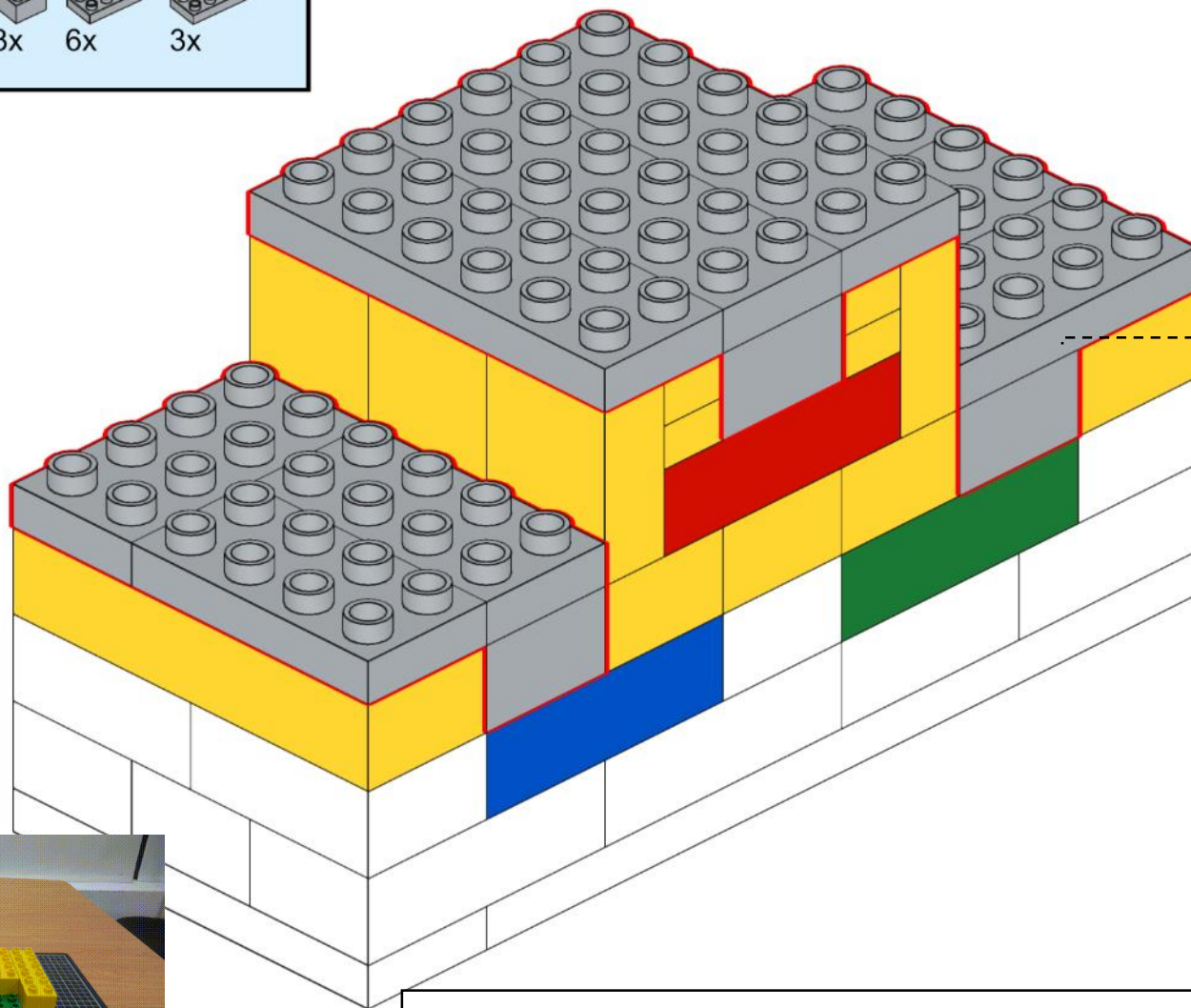
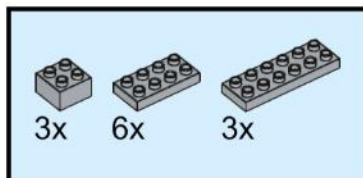
被曝光到的光阻劑會被沖洗掉，  
並進行**硬烤**。



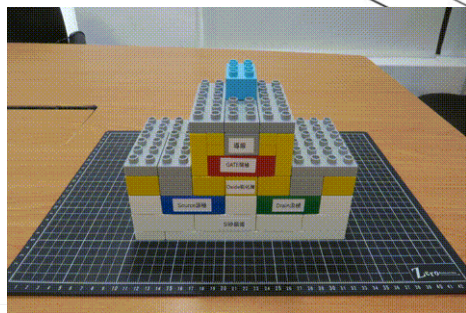
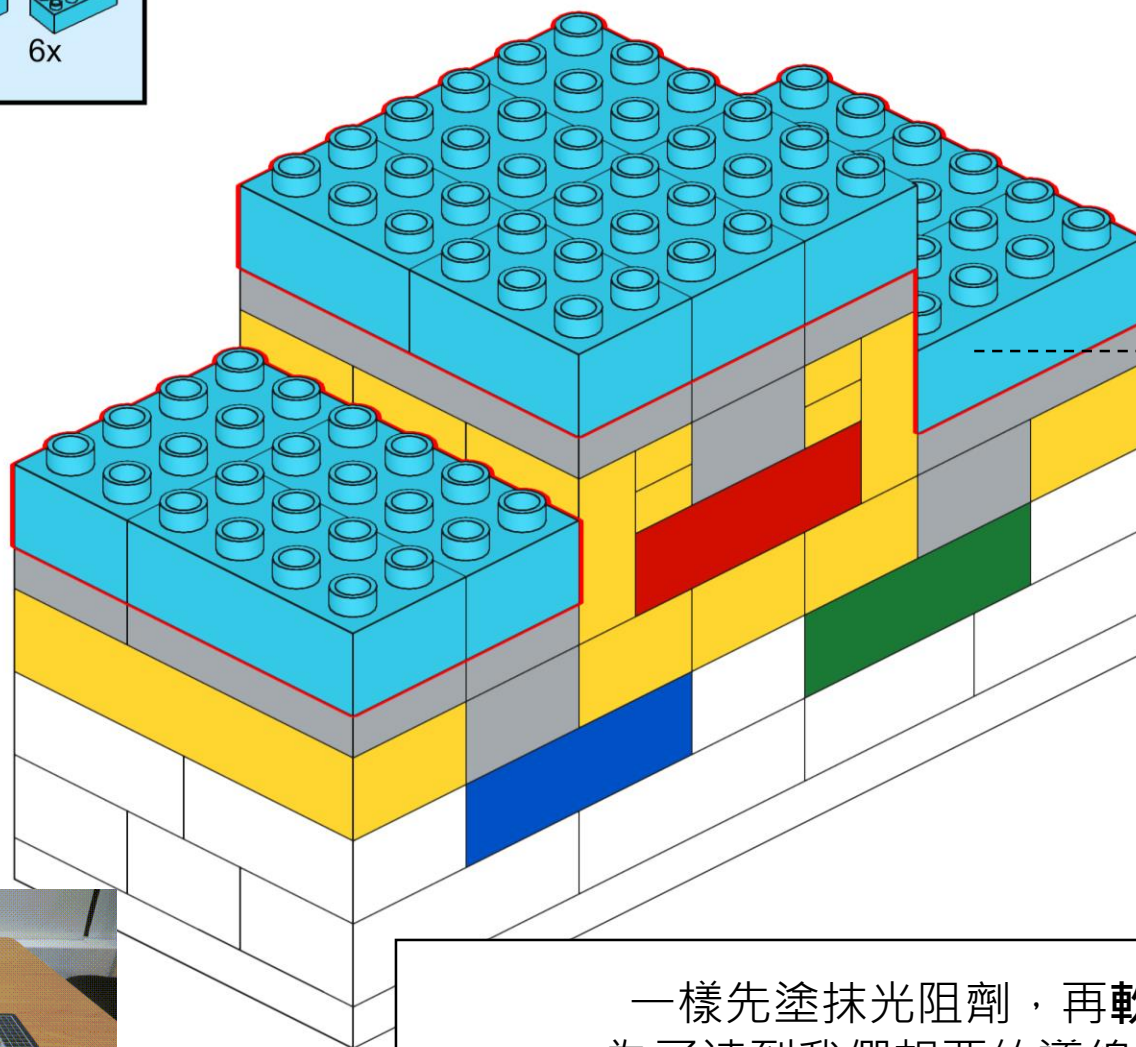
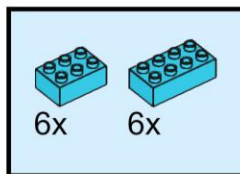
接著進行蝕刻，  
將下方的氧化層去除，  
如此就可以開出井窗。



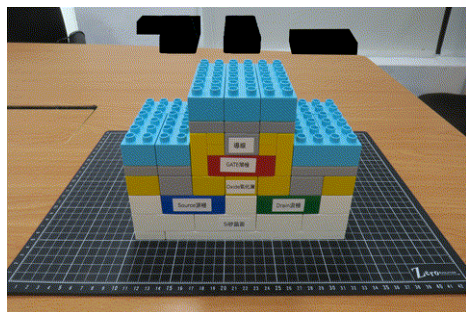
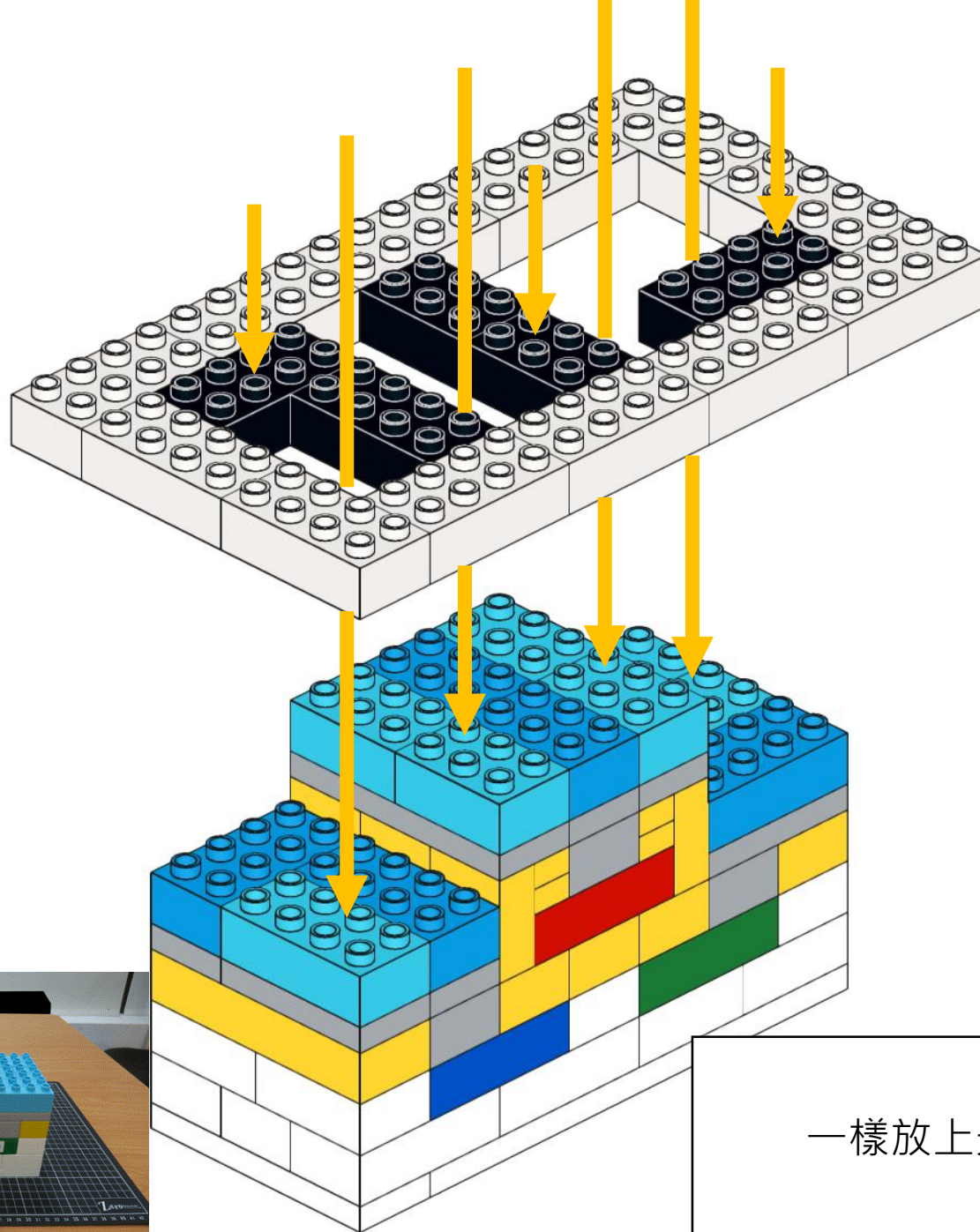
剩餘的光阻一樣去除掉。



透過金屬薄膜沉積，  
在表面形成金屬薄膜(像是鋁)。

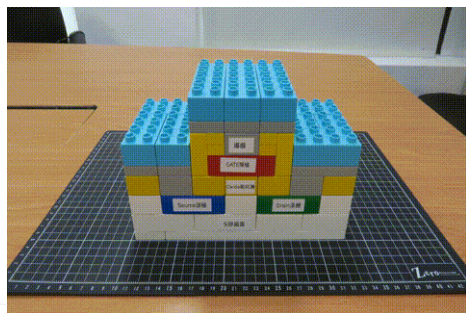
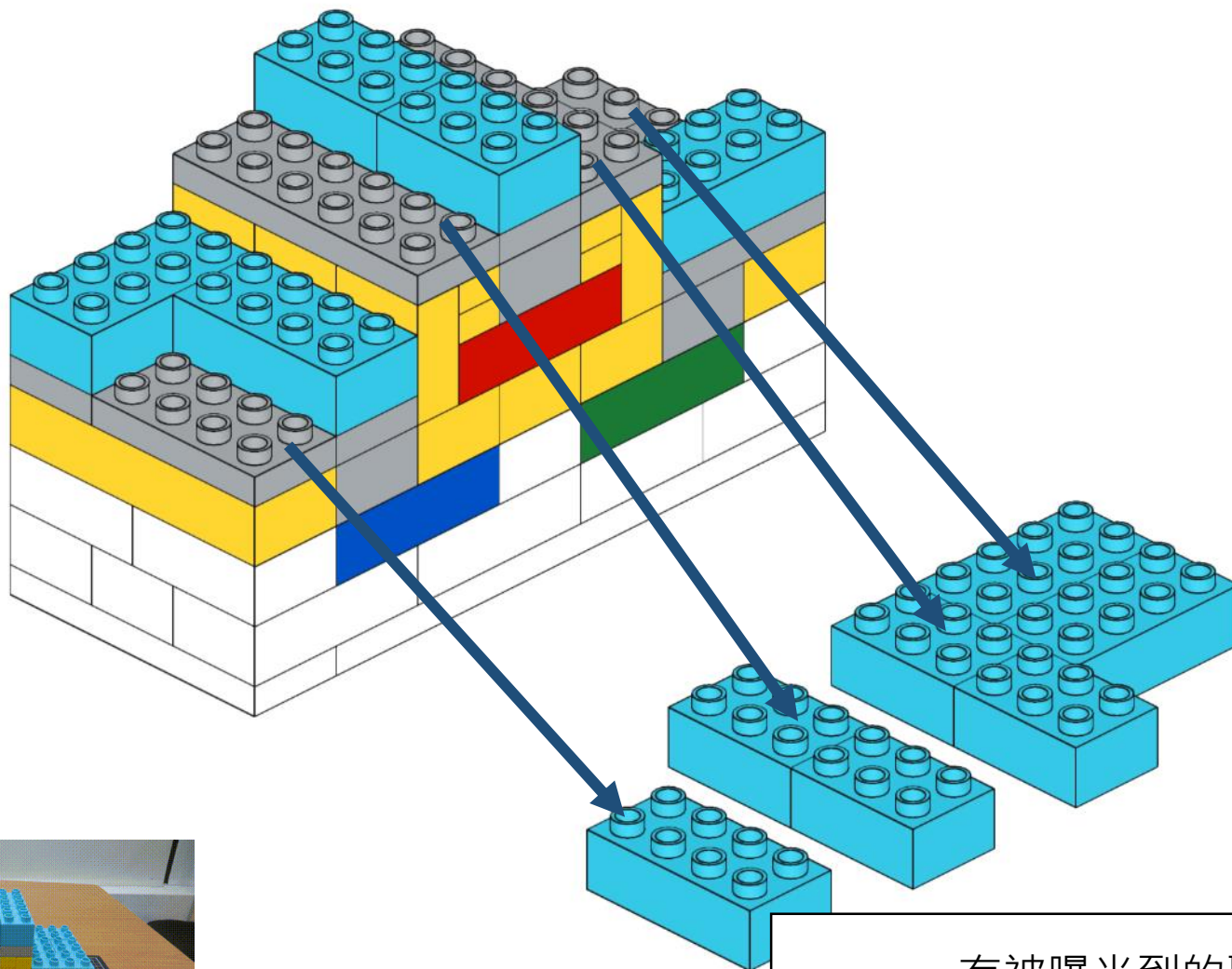


一樣先塗抹光阻劑，再**軟烤**。  
為了達到我們想要的導線線路，  
所以也需要利用蝕刻來達到我們想要得圖案(線路)。

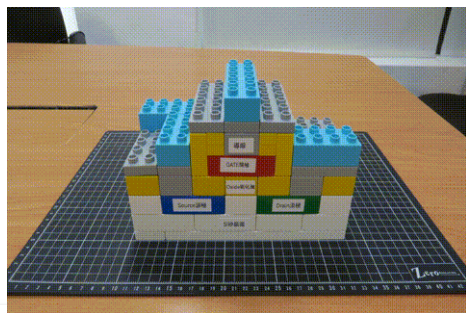
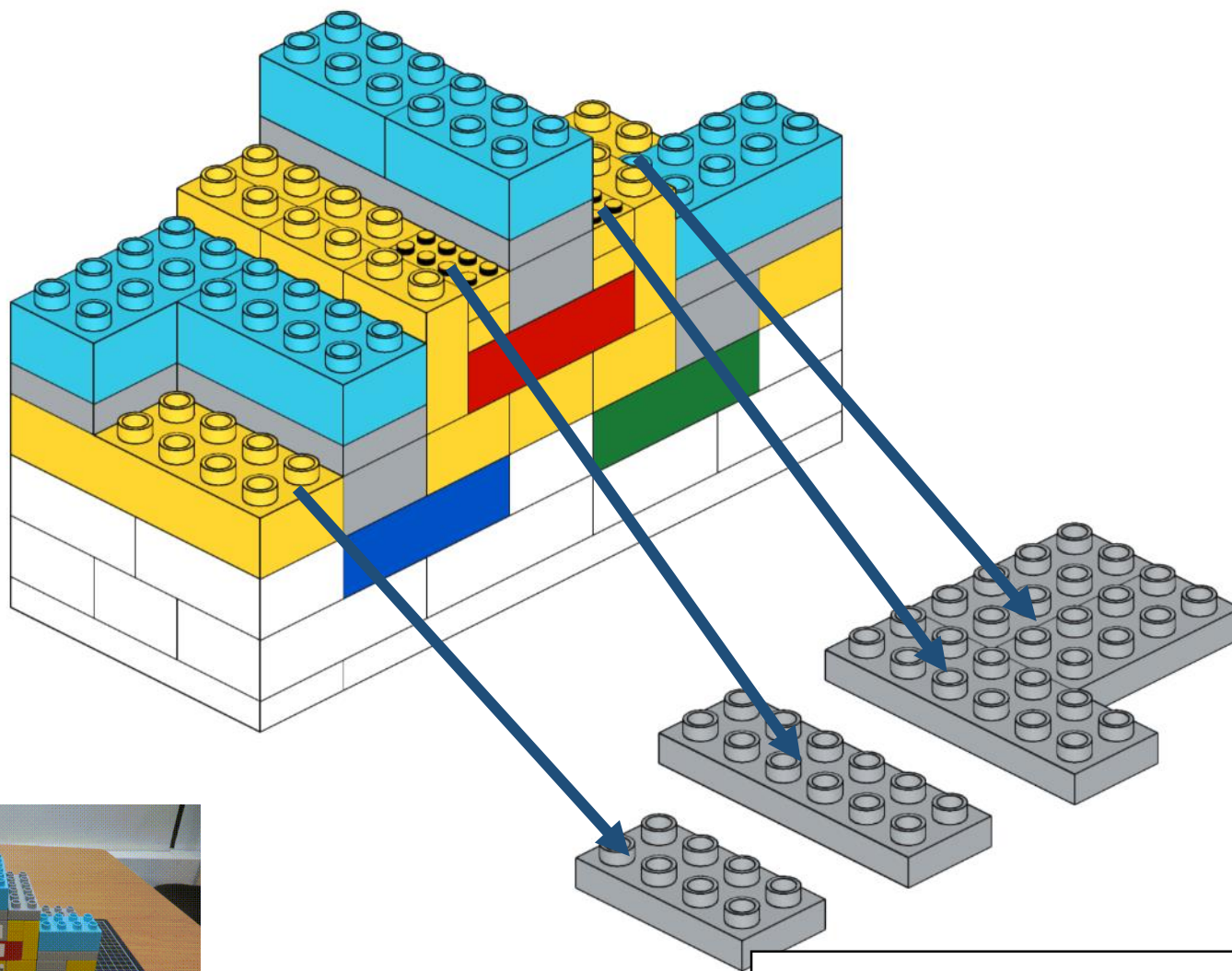


一樣放上光罩後並曝光。

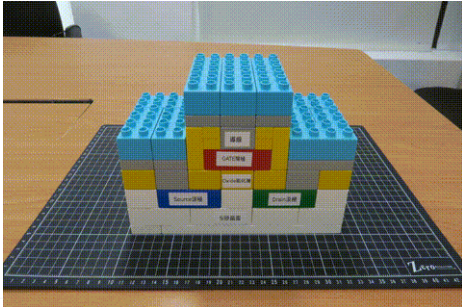
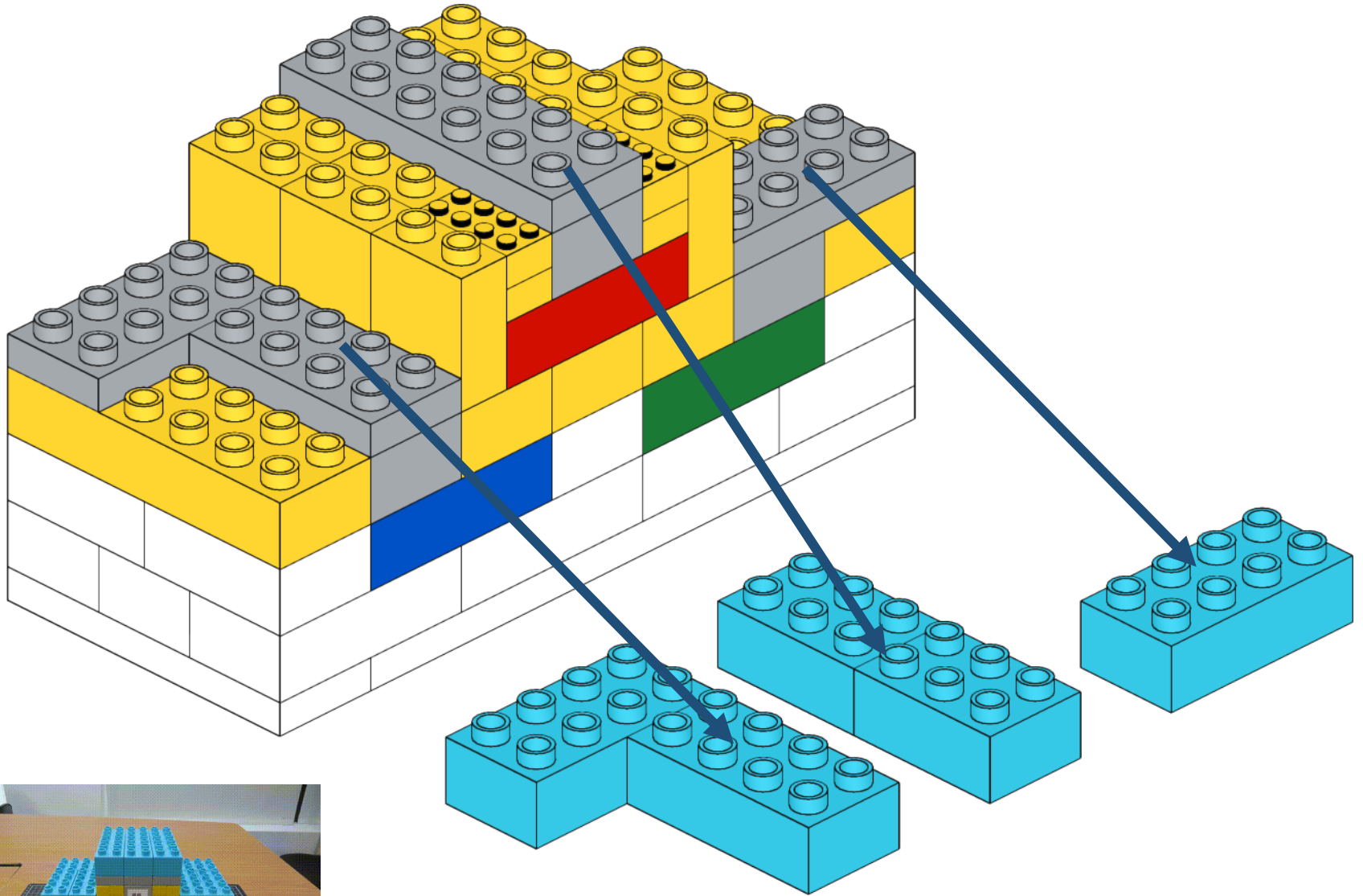




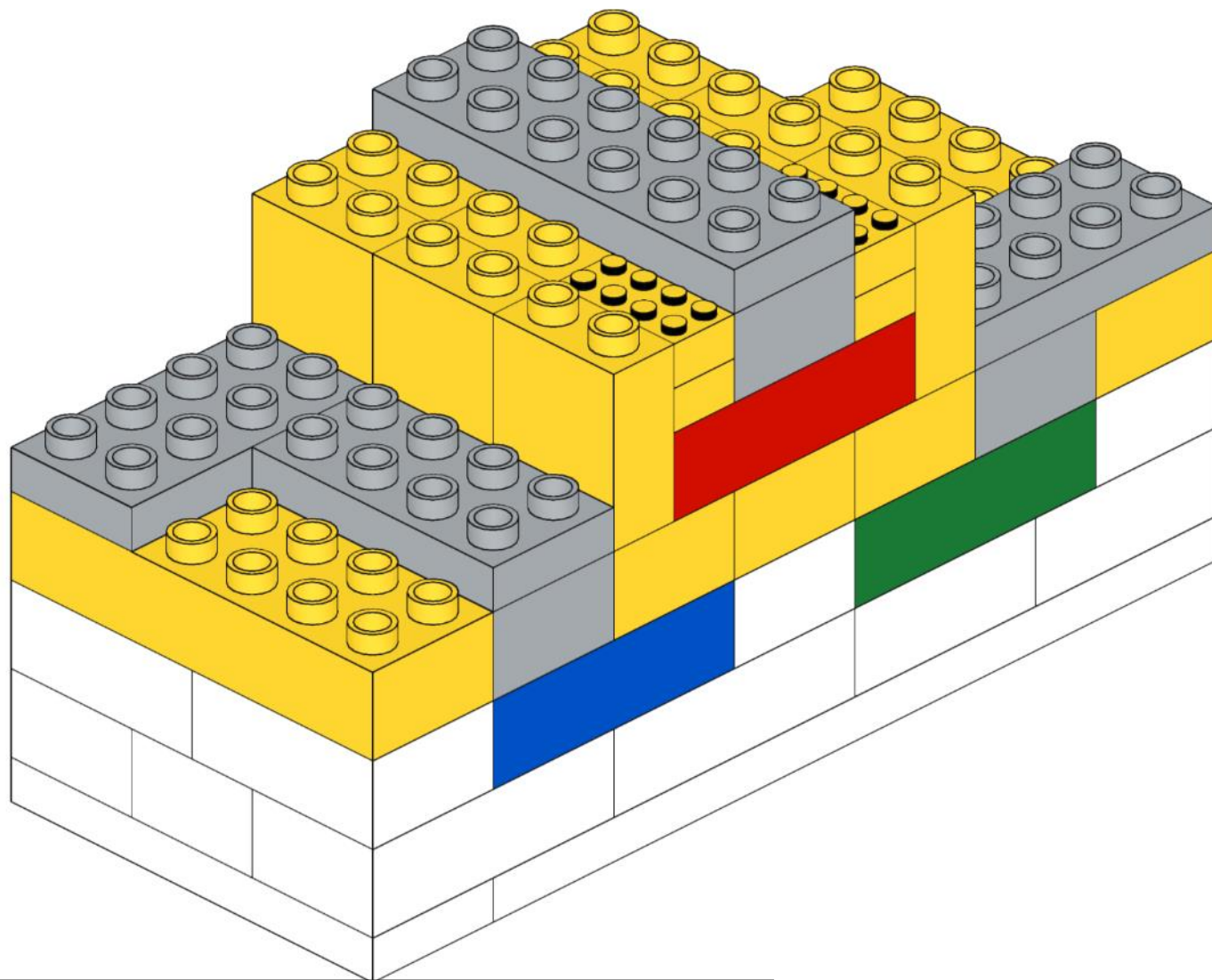
有被曝光到的區域  
可以被顯影劑沖洗掉。  
並進行**硬烤**。



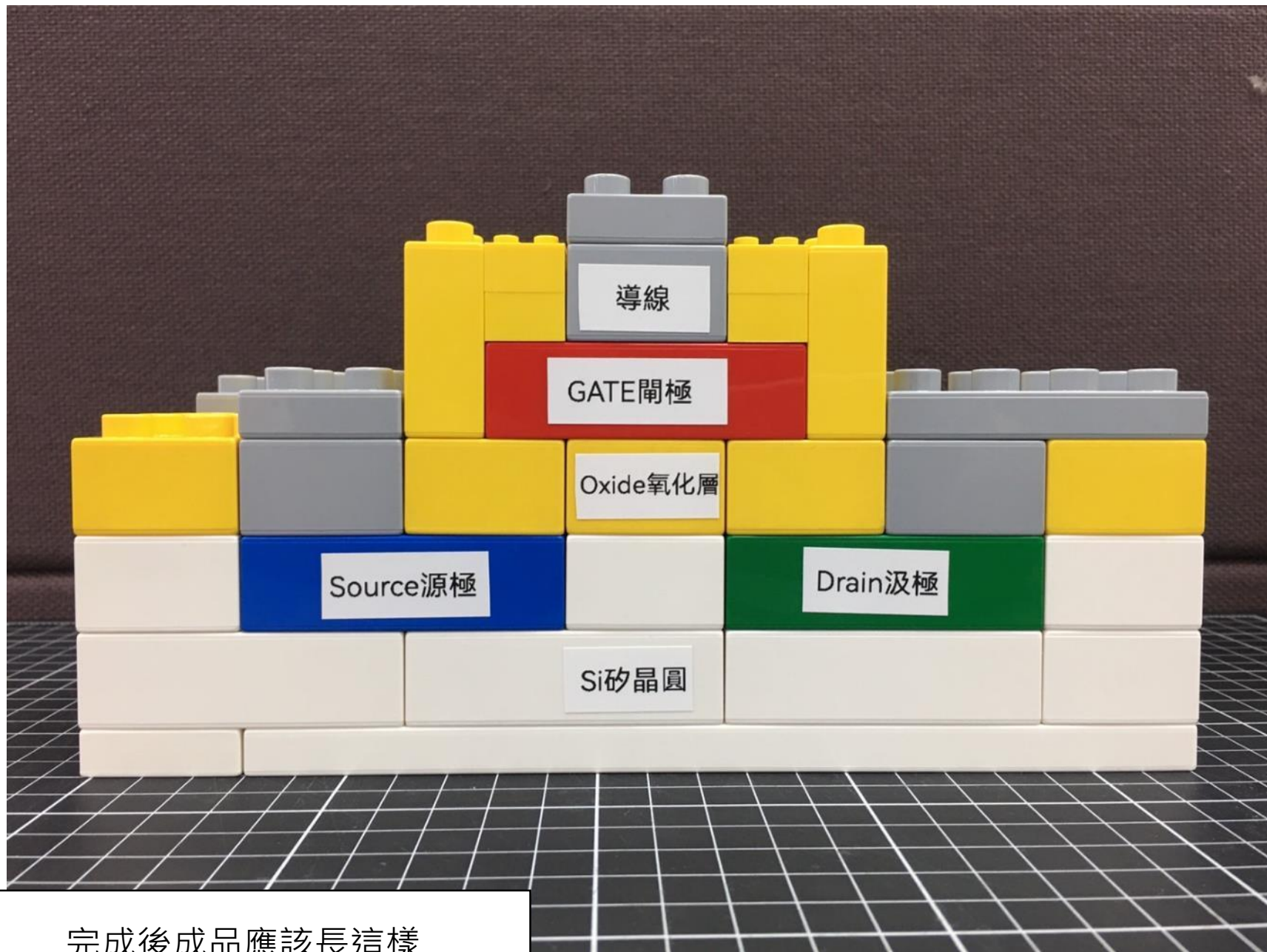
接著蝕刻掉不需要的金屬薄膜。



剩餘的光阻劑一樣去除掉。



這樣就完成了一個半導體元件 – 場效電晶體了！



完成後成品應該長這樣



YT link: [https://youtu.be/gnieAZq\\_-Gc](https://youtu.be/gnieAZq_-Gc)

**Thank you for your attention.**